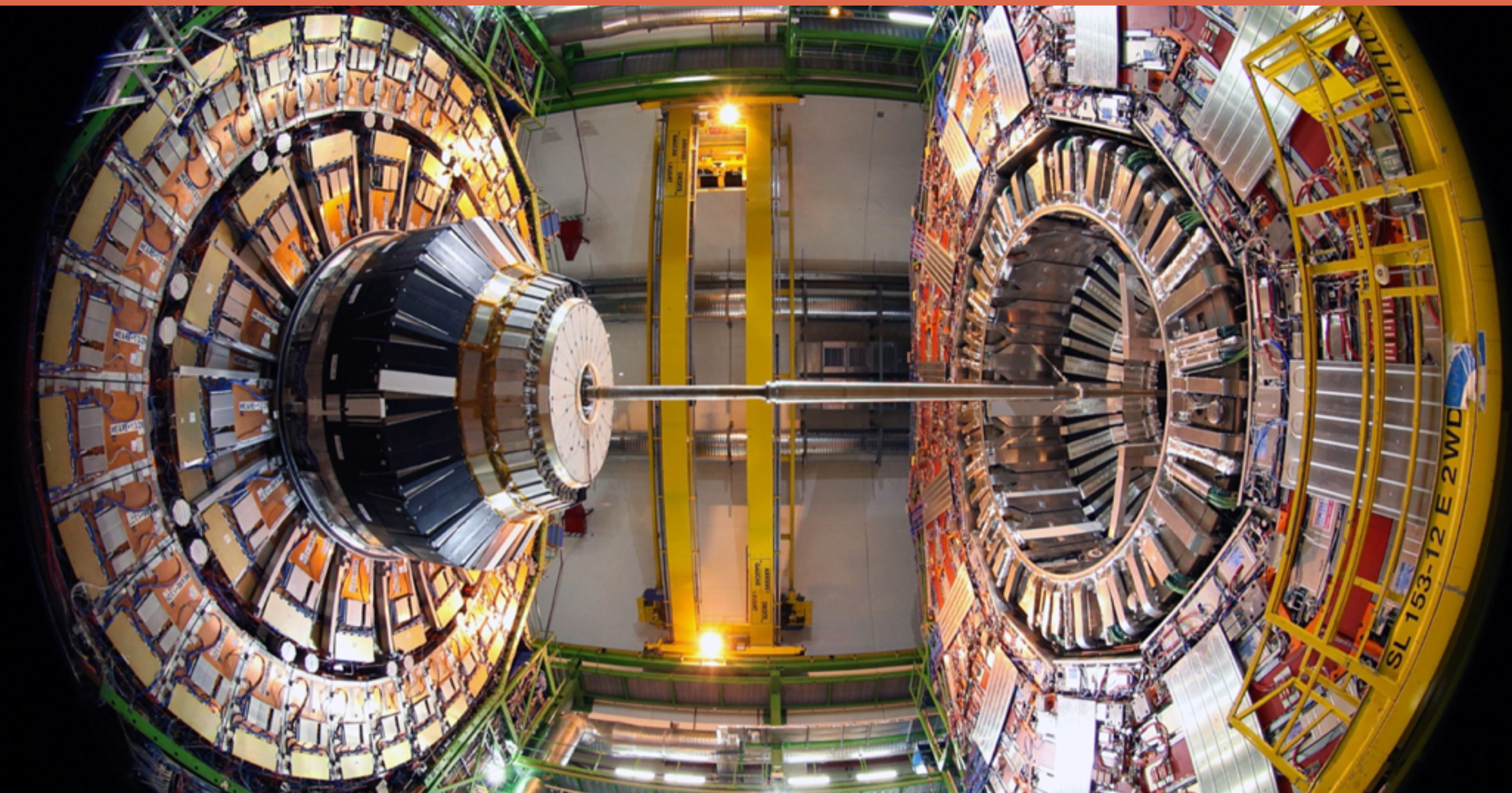


CMS Endcap Calorimeter Upgrade, HGCal



Zoltan Gecse  Fermilab

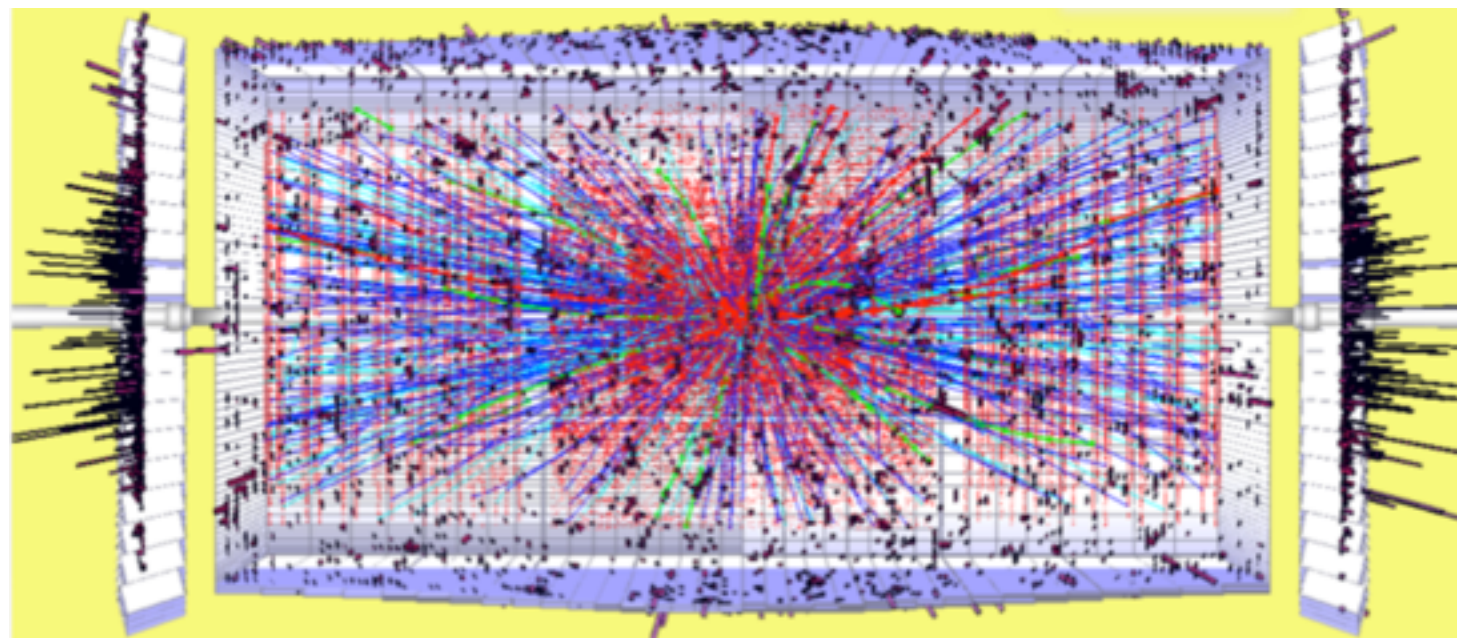
On behalf of CMS Collaboration

October 17, 2016, INFIERI

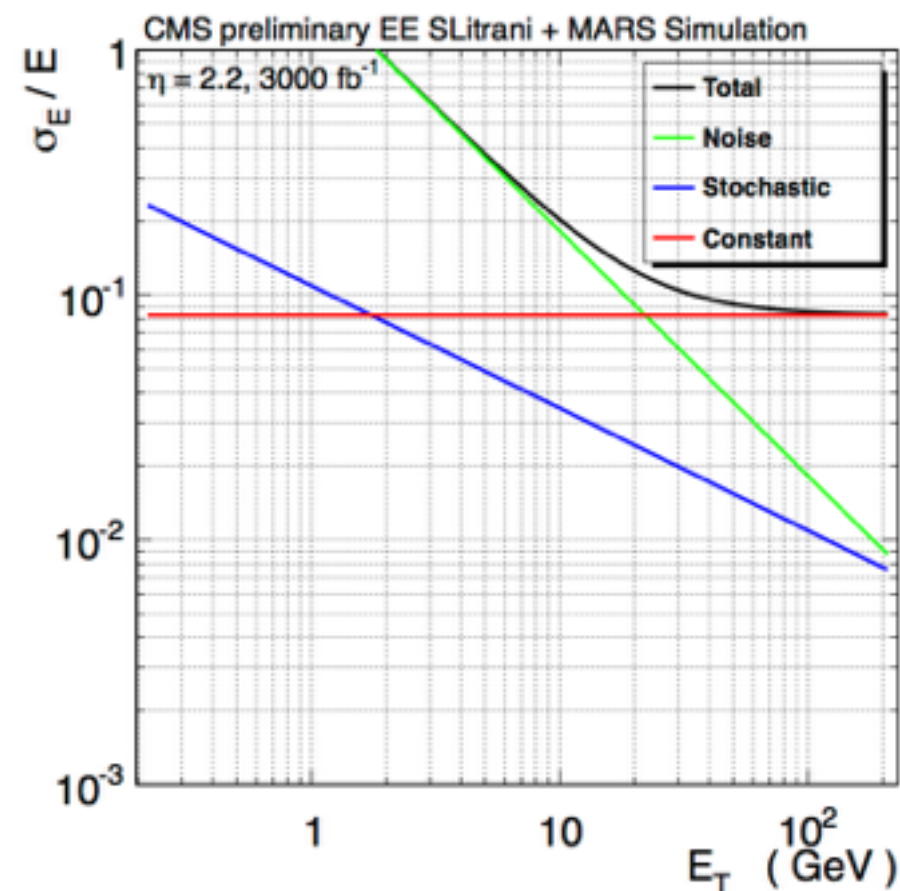
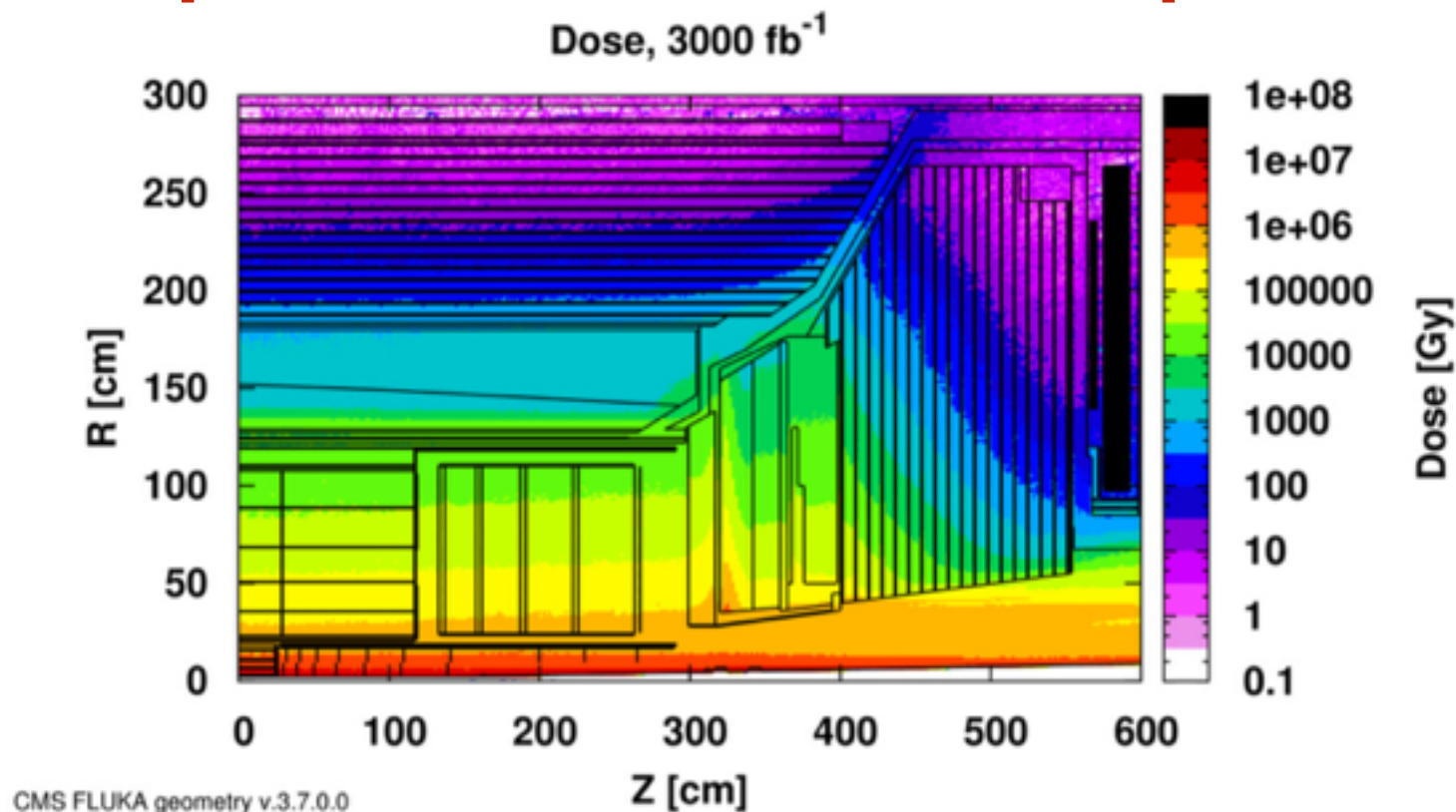
Challenges at HL-LHC

- HL-LHC plans $5e34/\text{cm}^2/\text{s}$ instantaneous luminosity and $3000/\text{fb}$ integrated

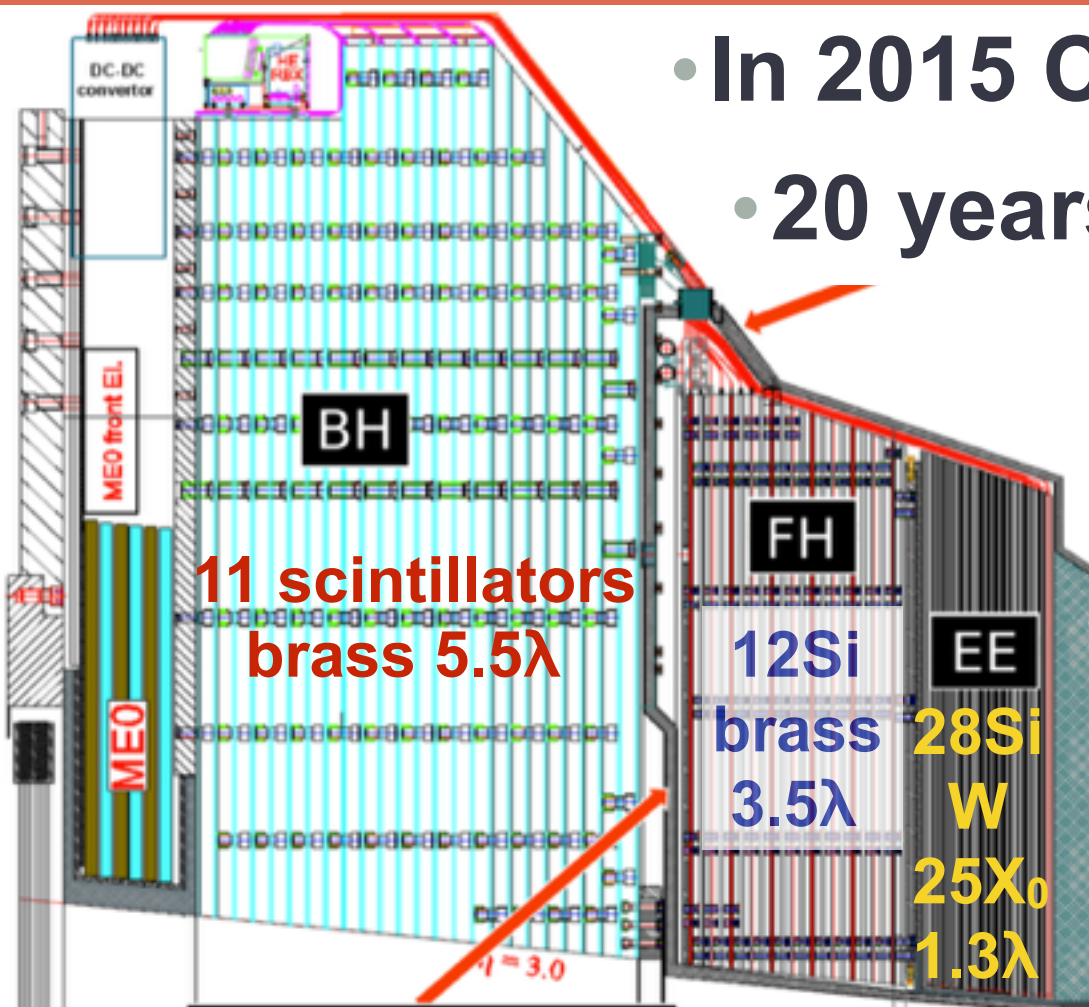
- High pile-up conditions (200 PU)
- High radiation dose (150Mrad , $10^{16}\text{n}/\text{cm}^2$)
- Resolution of current endcap EE increases to $O(10\%)$

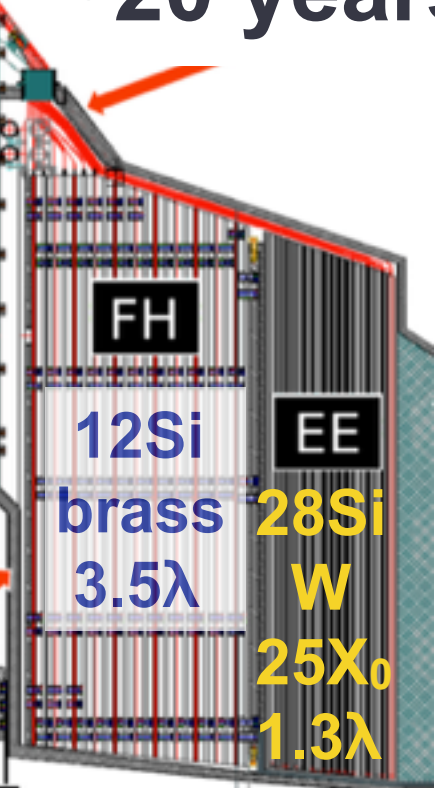


- **Endcap Calorimeter needs replacement**



The HGCal Endcap Design



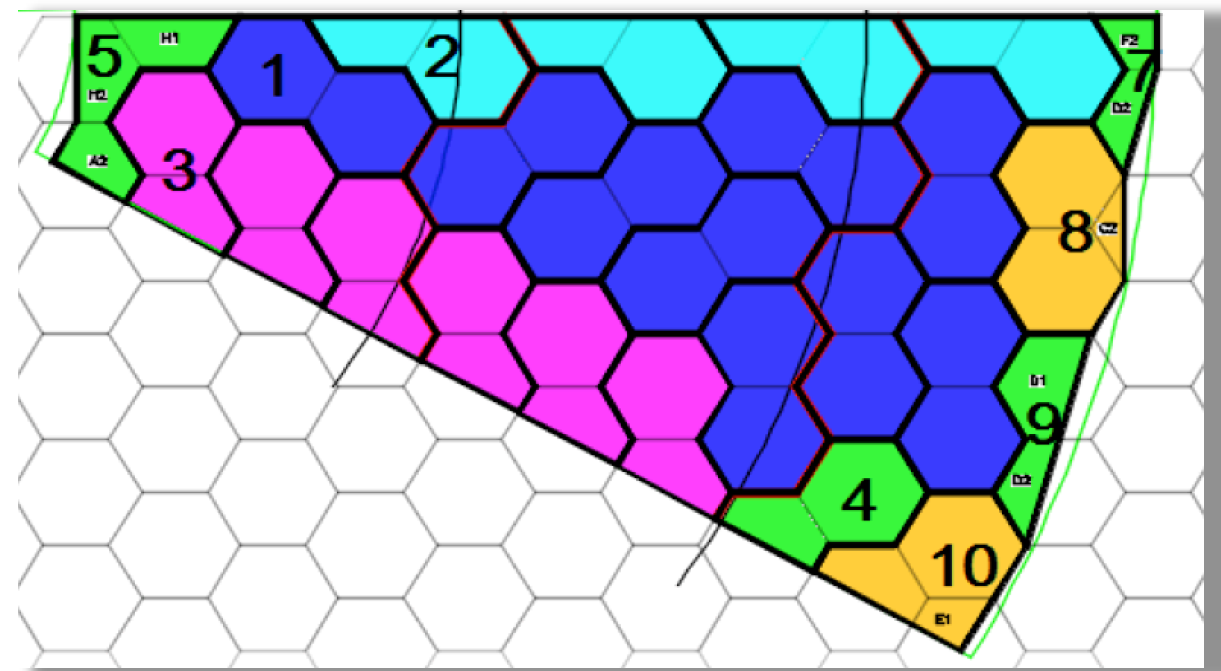
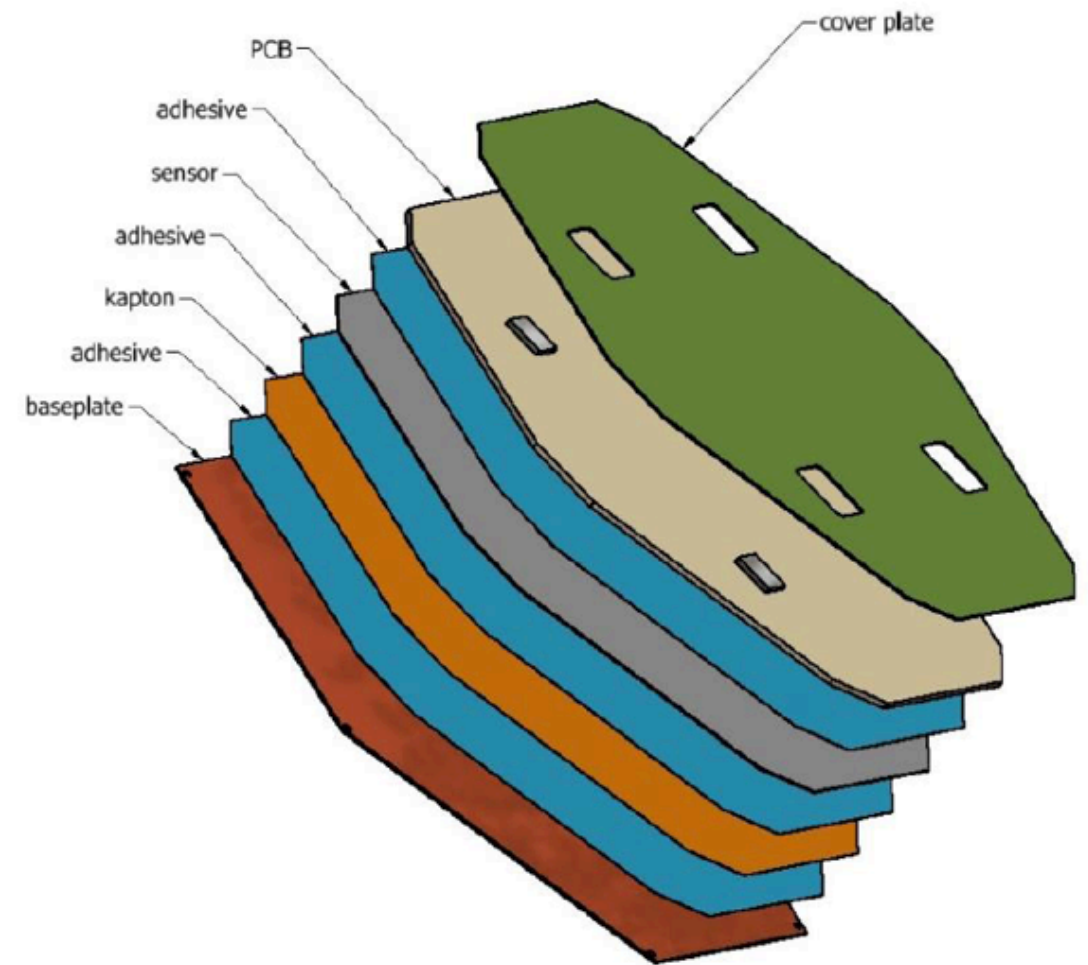
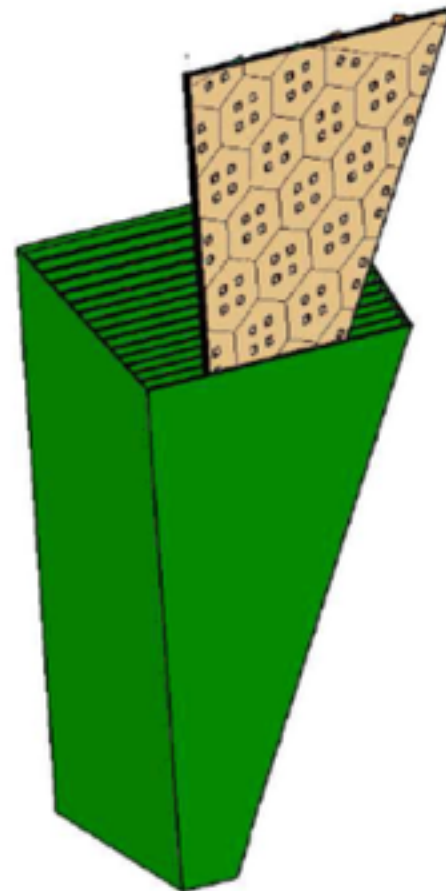
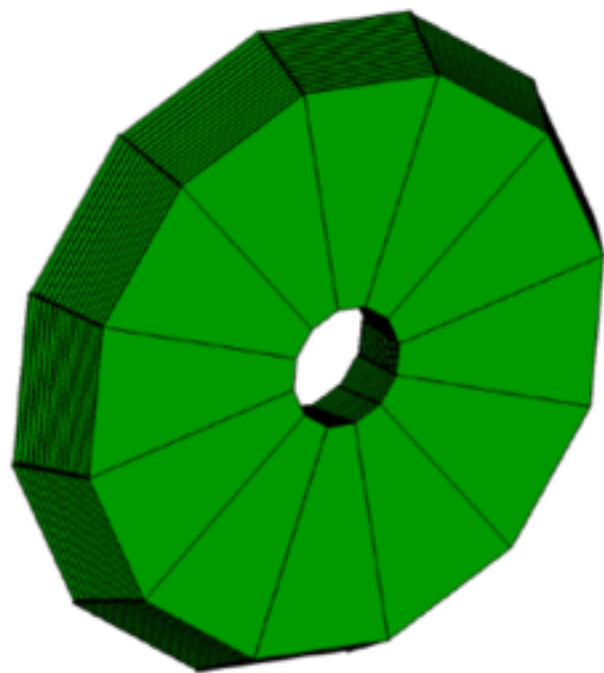
- In 2015 CMS chose a silicon based calorimeter
 - 20 years of experience from tracker and pixel
 - Radiation effects are well understood and manageable with -30C temperature operations
 - High granularity and fast timing capability help mitigate pile-up
 - Electronics in 130/65nm allows low noise and low power readout even for large dynamic range
- 
- The diagram illustrates the layered structure of the CMS calorimeter. It shows a cross-section with various materials and their thicknesses relative to the radiation length (λ). The layers include:
- FH** (Front Face) at the top.
 - 12Si** (12 Silicon) layer.
 - brass** layer.
 - 3.5 λ** (3.5 radiation lengths) for the brass layer.
 - 28Si** (28 Silicon) layer.
 - W** (Tungsten) layer.
 - 25 X_0** (25 nuclear interaction lengths) for the tungsten layer.
 - 1.3 λ** (1.3 radiation lengths) for the final silicon layer.
 - EE** (Endcap Electronics) on the right side.
- Red arrows indicate the path of particles entering the calorimeter from the top left.

- **Key parameters:**

- 600 m² of silicon
- 6M readout channels, 0.5-1 cm² area cells
- 21660 modules (8" or 2x6" sensors)
- 115kW power at end of life

Construction

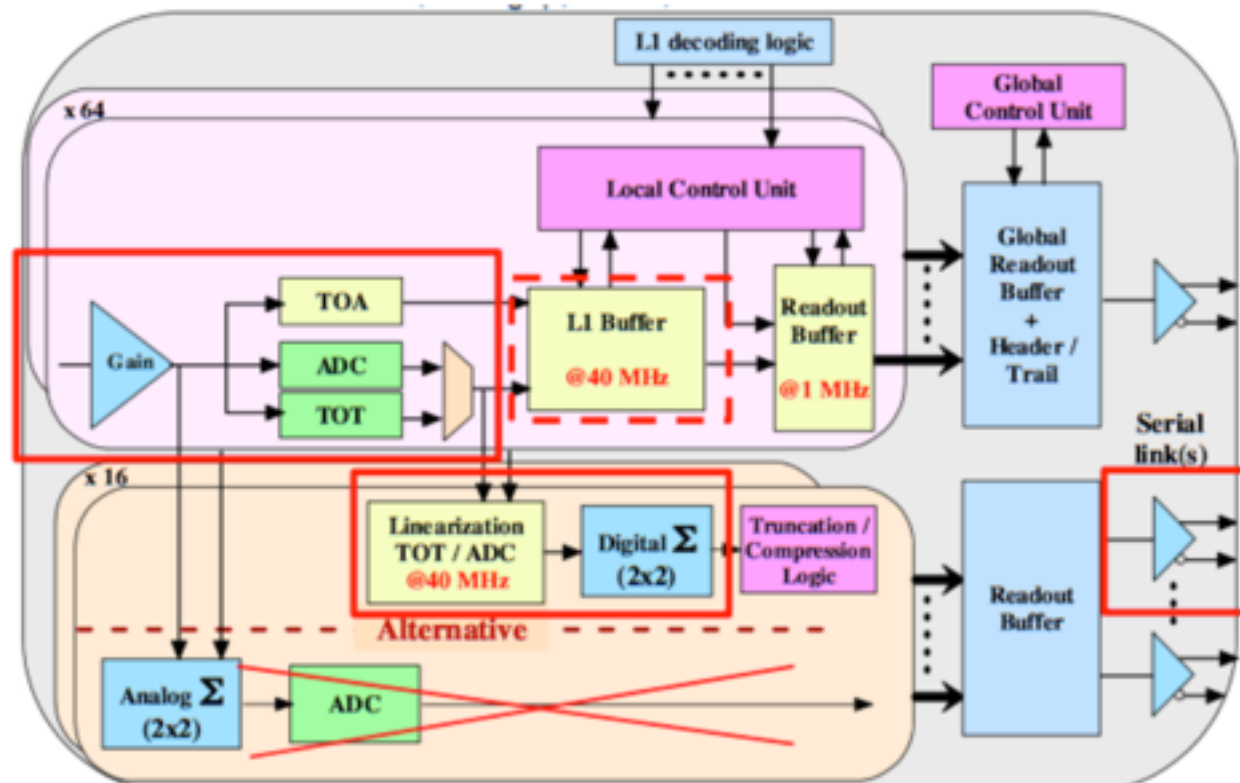
- Modules built from W/Cu baseplate, hexagonal sensors and readout PCB
- Cassettes built from modules and Cu cooling plate
- Cassettes inserted into absorber



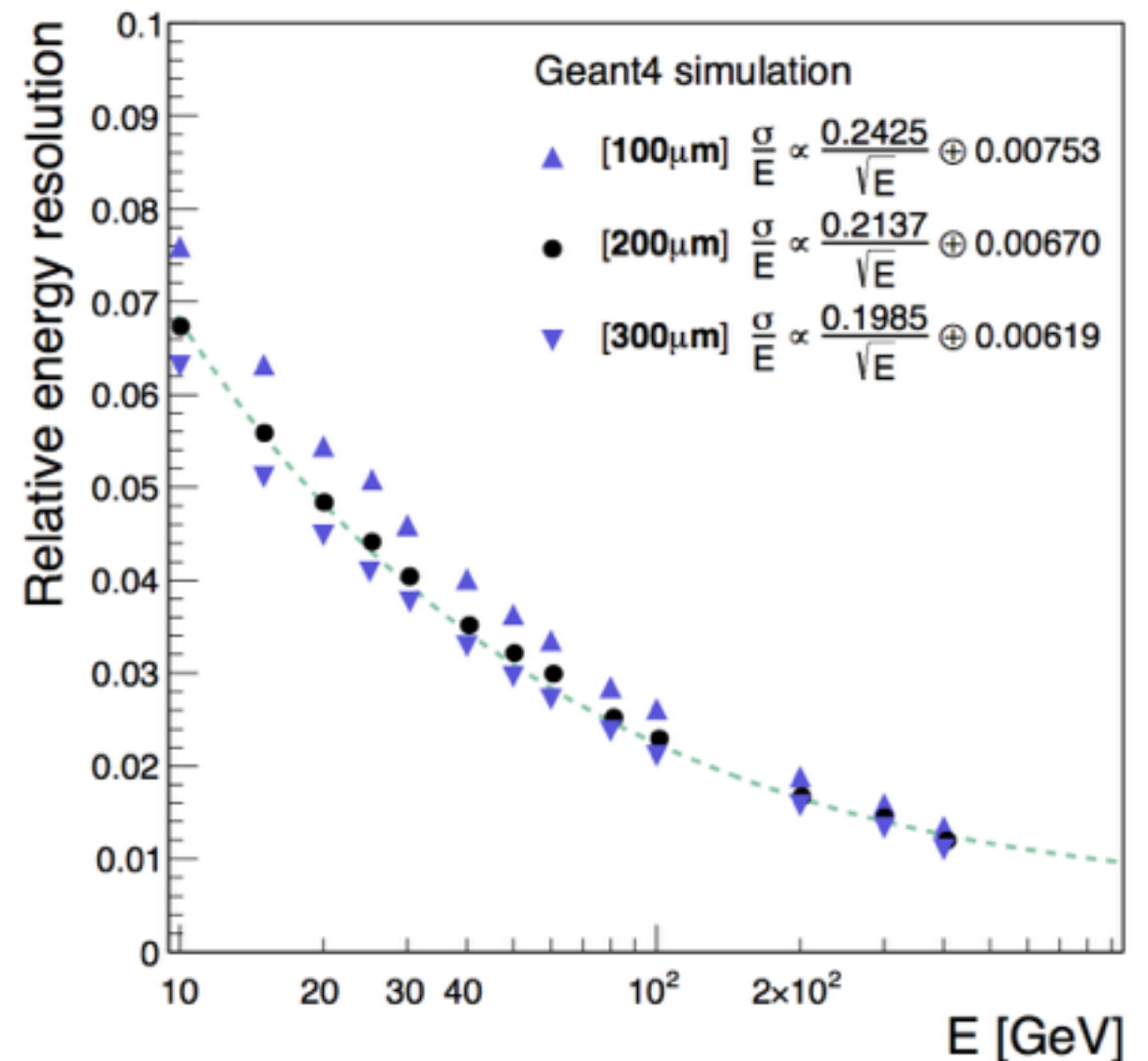
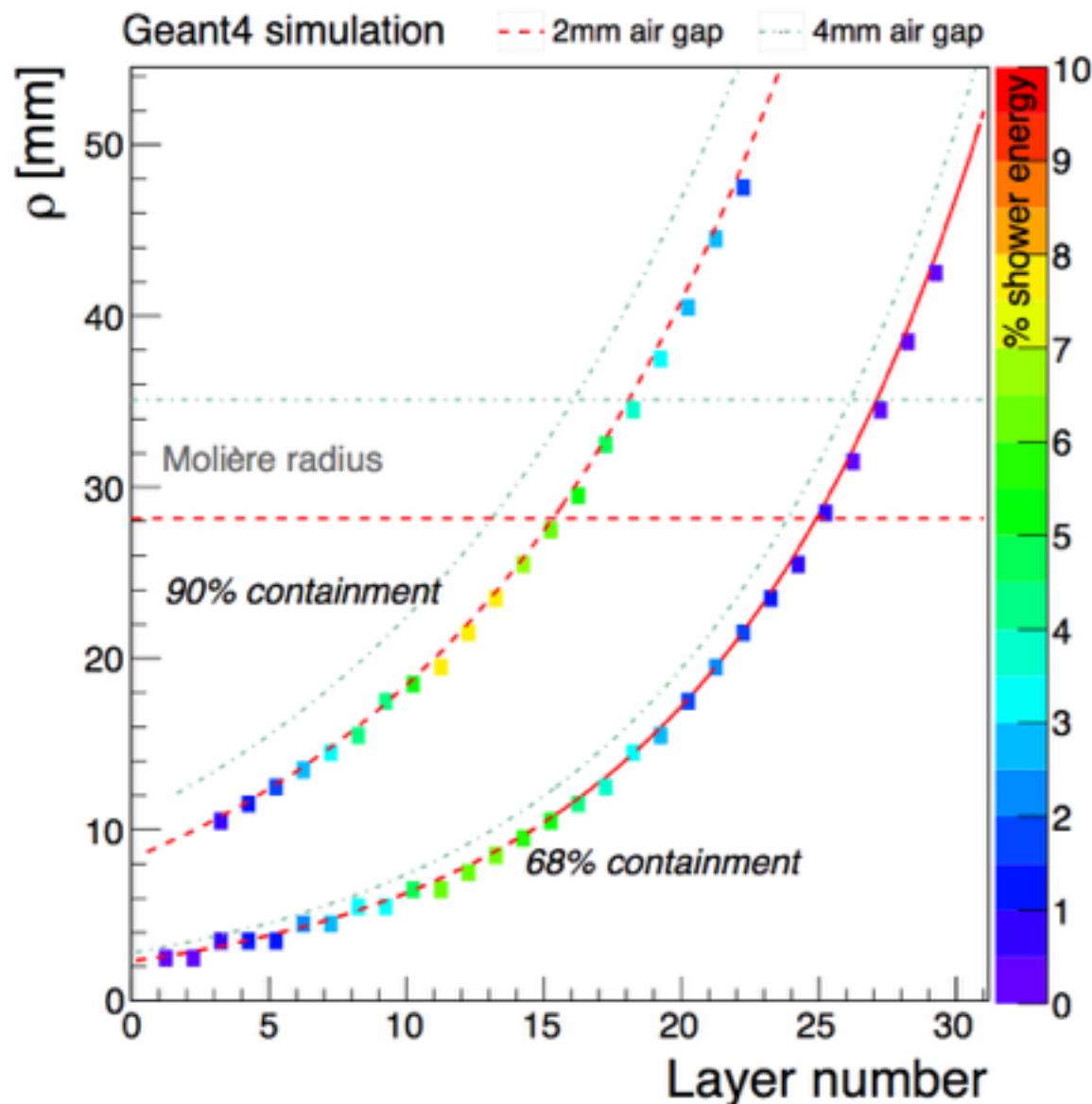
Front-end Electronics

Very stringent requirements for Front-End Electronics

- Large dynamic range 0.4 fC – 10 pC (15 bits)
noise < 2000 e- to keep MIP visibility for low thickness sensors after 3000 fb⁻¹
- Leakage current compensation
- Low power budget < 10 mW/channel
- Timing information 50 ps accuracy
- System on chip (digitization, processing), high speed readout (>Gb/s), large buffers to accommodate 12.5μs latency of L1 trigger
- Preferably compatibility for positive and negative inputs.
- High radiation resistance (150 MRad, 10¹⁶ n/cm²)



Expected Performance



• Electromagnetic showers narrow

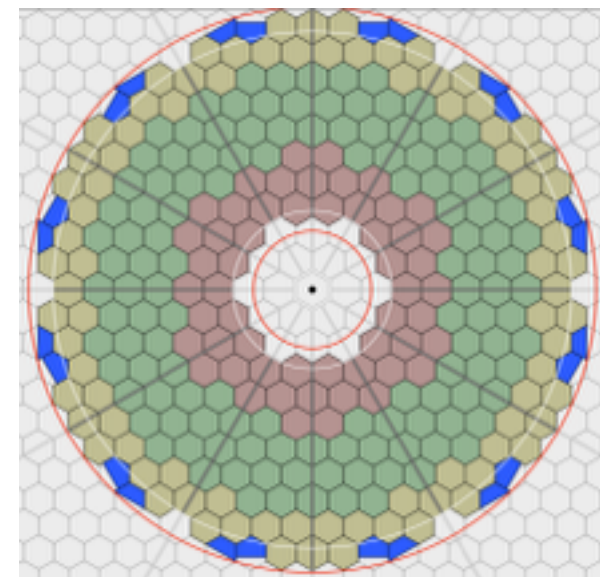
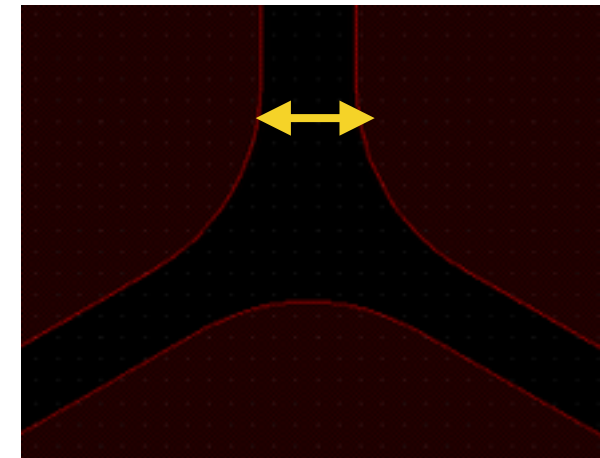
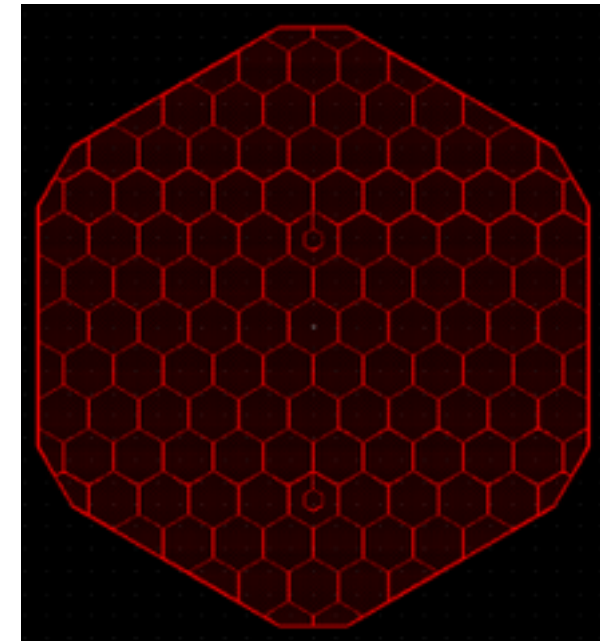
- pile-up rejection
- good separation for particle flow approach
- minimize thickness in design

• Energy resolution EM

- stochastic term ~20%
- target constant term < 1%

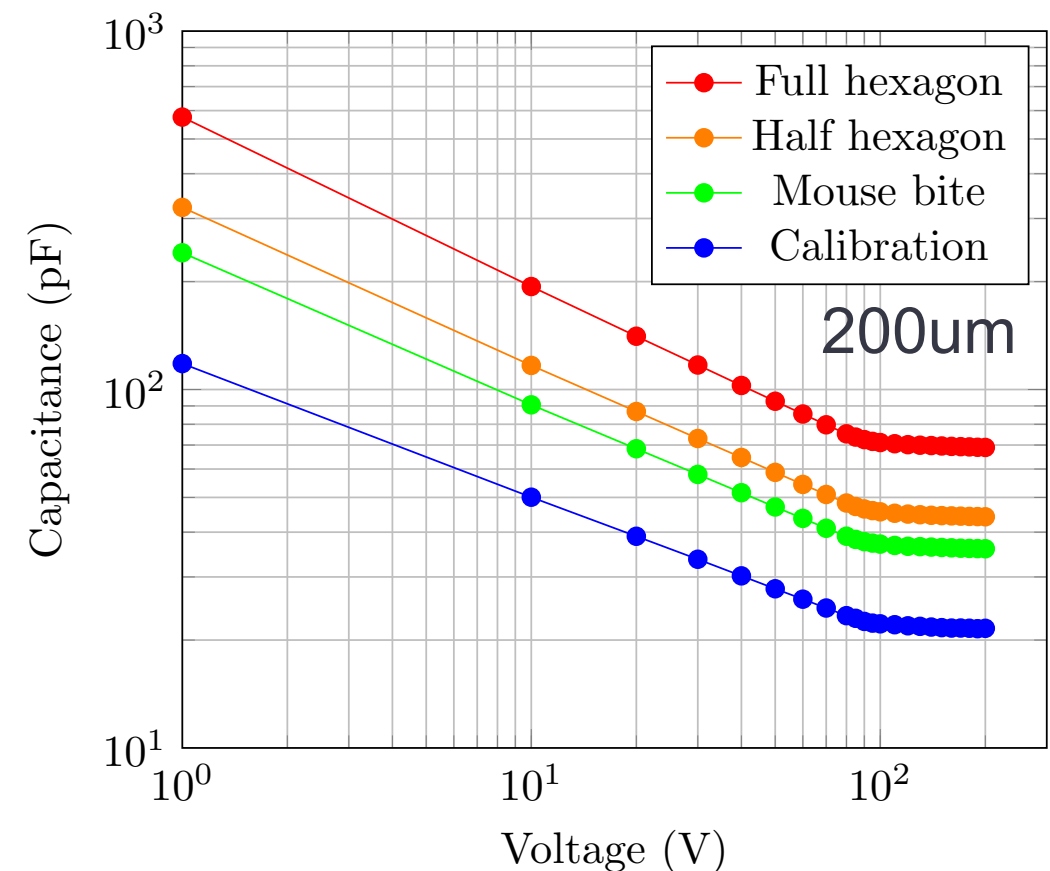
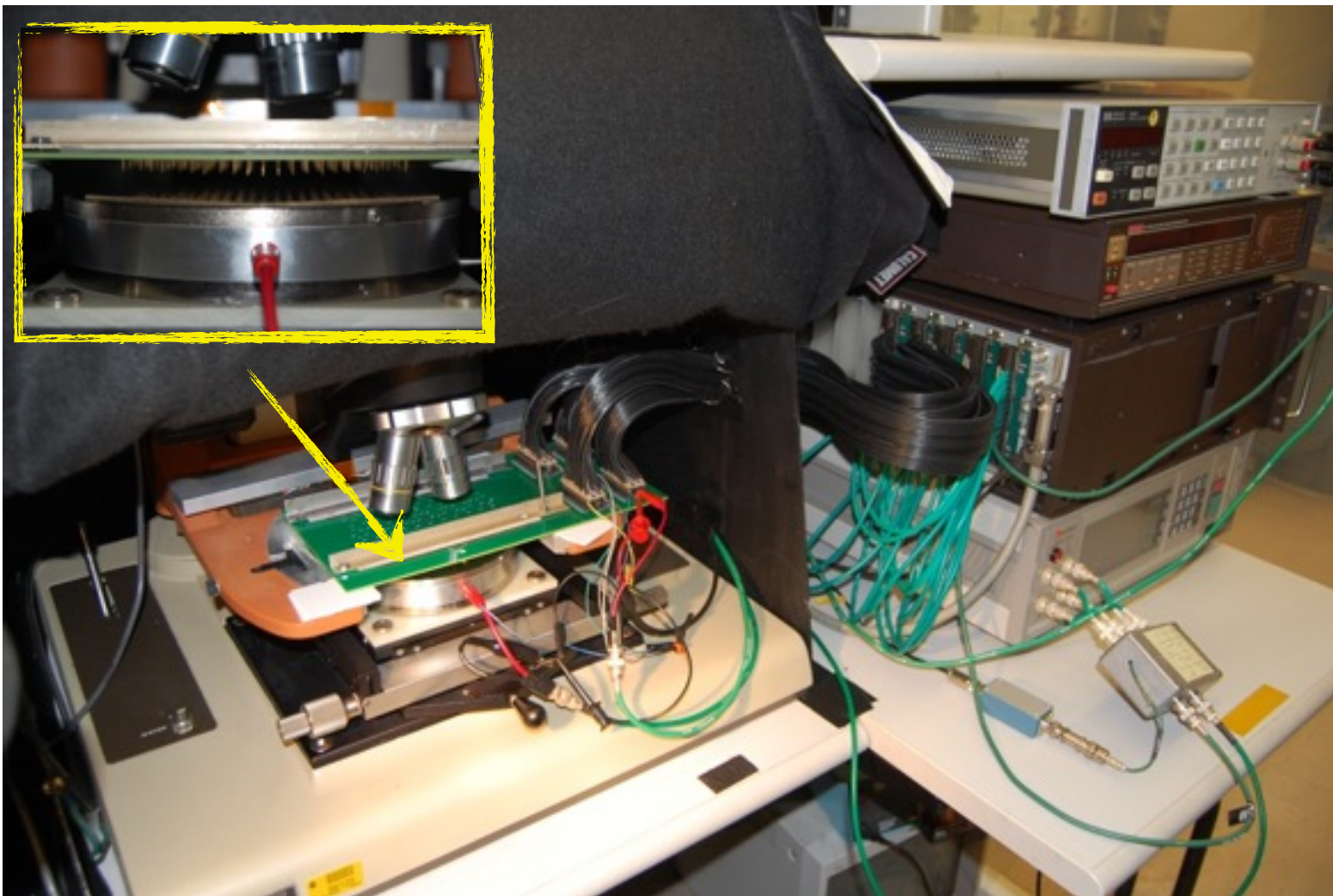
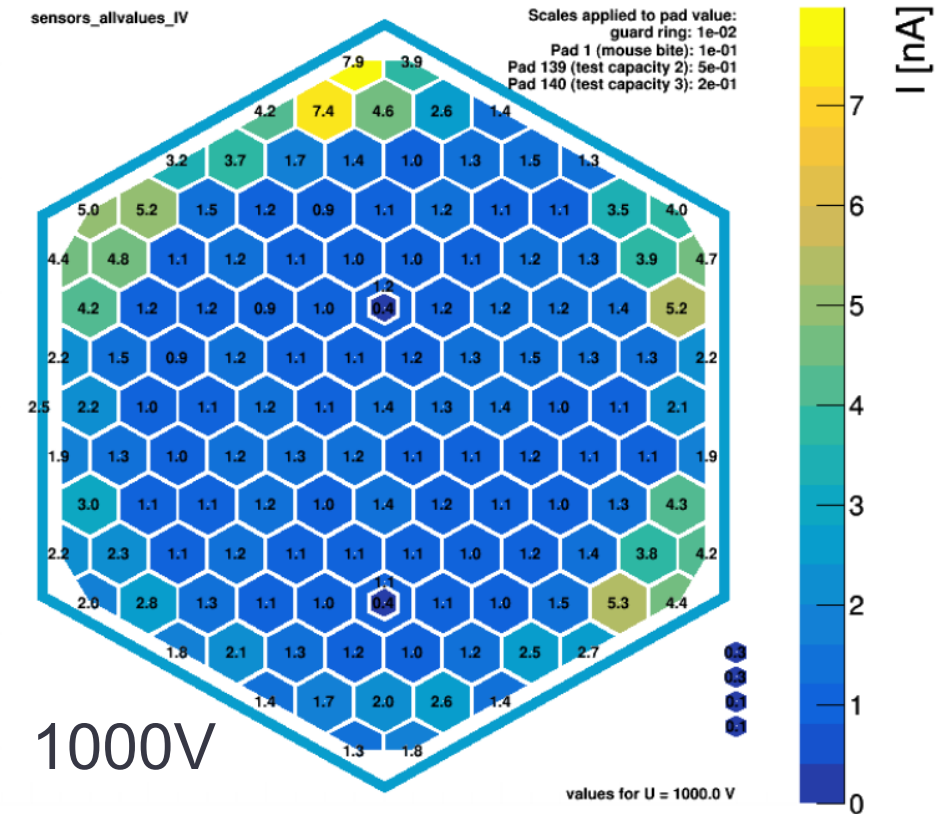
Silicon Sensor R&D

- **Hexagonal sensors from 6" vs 8" wafers**
 - 8" wafers offer lower costs
- **Inter cell distance (20um - 80um)**
 - The larger the distance the smaller the inter-cell capacitance
 - The smaller the distance the larger the break down voltage
- **p-type vs n-type**
 - n-type are cheaper but at highest fluences less radiation tolerant
- **Active layer thickness (100um - 300um)**
 - at high fluences thinner ~100um sensors give more absolute collected charge than 200 or 300um ones
- **Comparison of performance of sensors from various vendors**
 - HPK: 6" n-type fabricated and tested, p-type to be ordered
 - Infineon and HPK: 8" p-type are being fabricated
 - Novati: half of 6" p-type from 8" wafer being tested



HPK Sensor Testing at Fermilab

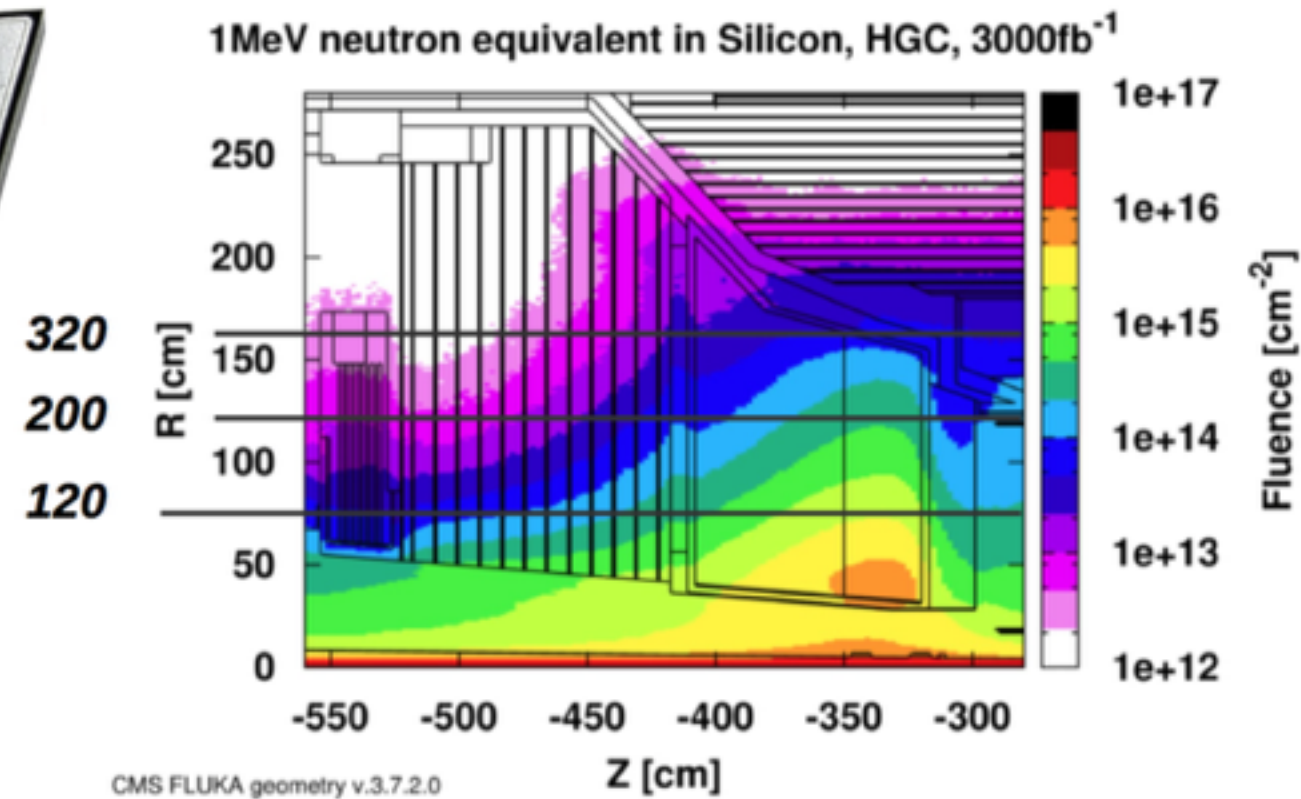
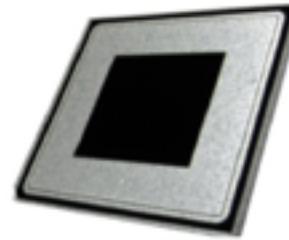
- **Prototype 6" n-type sensors from HPK**
 - Testing with custom probe card, contacting all channels with spring loaded pins
 - 50 tested sensors showed expected performance and excellent quality: no breakdown till 900V



Irradiation Studies of Si Diodes

• Types of diodes

- Silicon growth technique:
dd-FZ: float zone deep diffusion
Epi: epitaxial layer
- n-on-p (p type), p-on-n (n-type)
- Active thickness: 50um - 320um
- Size: 5mm x 5mm



• Goal: investigate performance after neutron irradiation up to $1.5e16$ n/cm²

List of sensors and status:

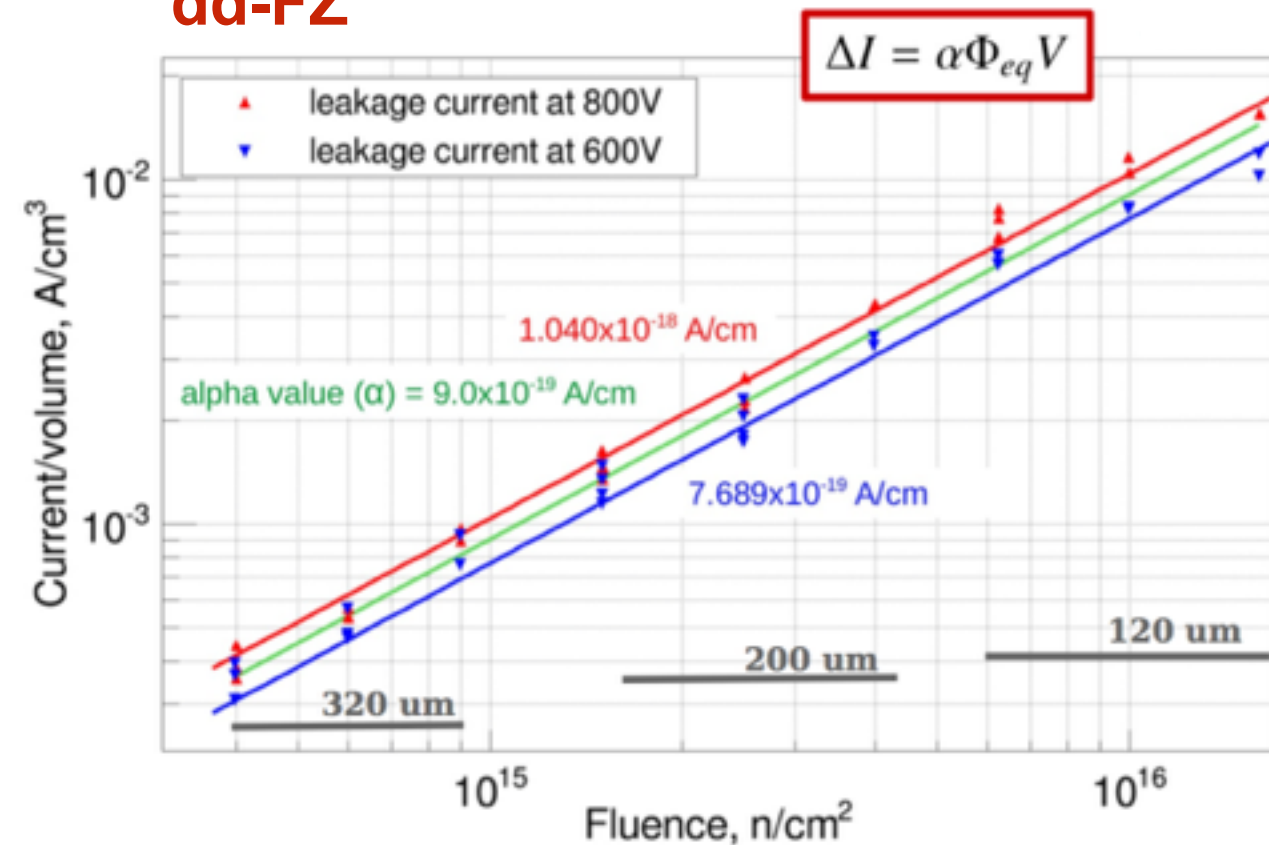
Fluence n/cm2	Thickness (um)				
	Float zone		Epitaxial		
	320	200	120	100	50
4.00E+014	1 n-on-p, 1 p-on-n				
6.00E+014	2 n-on-p, 2 p-on-n				
9.00E+014	1 n-on-p, 1 p-on-n				
1.50E+015		1 n-on-p, 1 p-on-n			
2.50E+015		2 n-on-p, 2 p-on-n			
4.00E+015		1 n-on-p, 1 p-on-n			
6.25E+015			2 n-on-p, 2 p-on-n	2 n-on-p	
1.00E+016			1 n-on-p, 1 p-on-n	2 n-on-p	2 n-on-p, 2 p-on-n
1.60E+016			1 n-on-p, 1 p-on-n		2 n-on-p, 2 p-on-n

Radiation Hardness Results

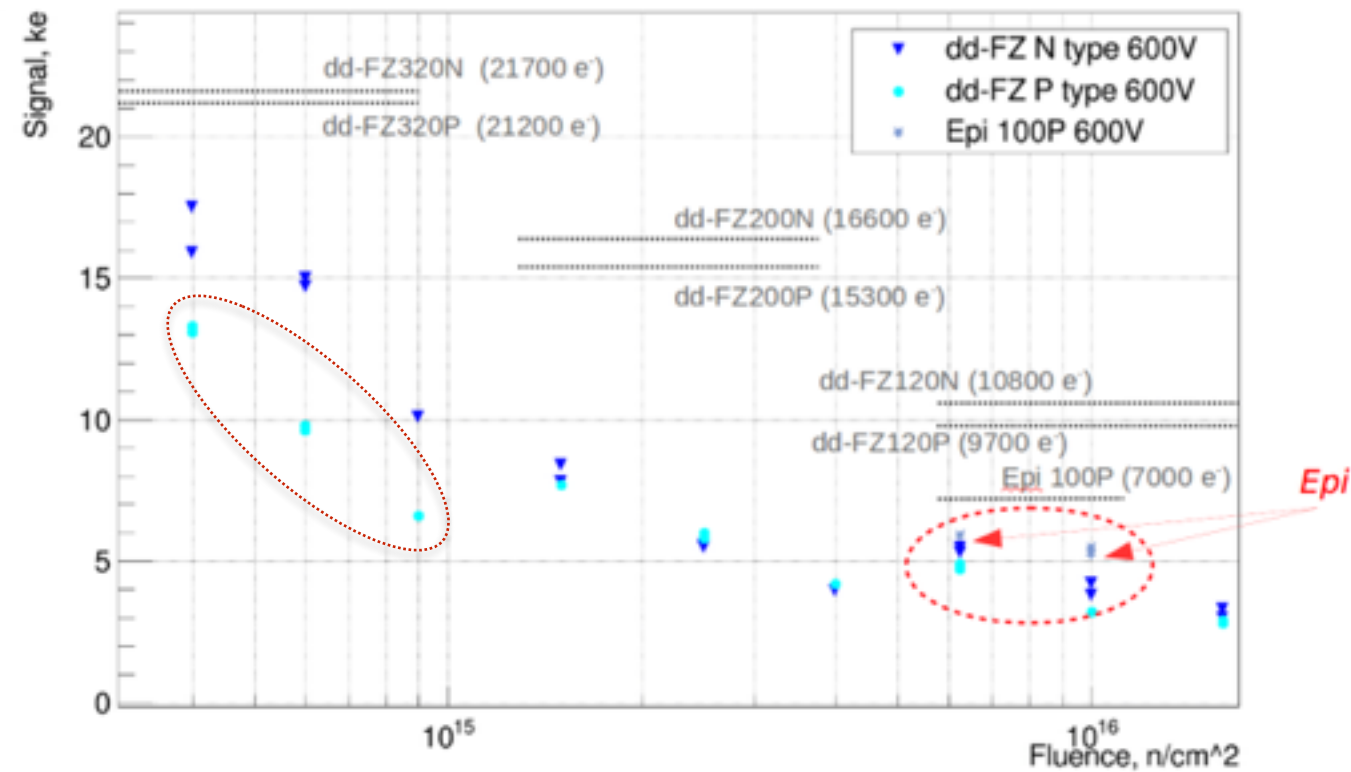
Signal injected with IR laser, confirmed with ^{90}Sr

-20°C and annealing of 10min@60°C

dd-FZ



Signal from CCE, TCT-IR-1063-250ps, T:-20°C, annealing 10min@60°C

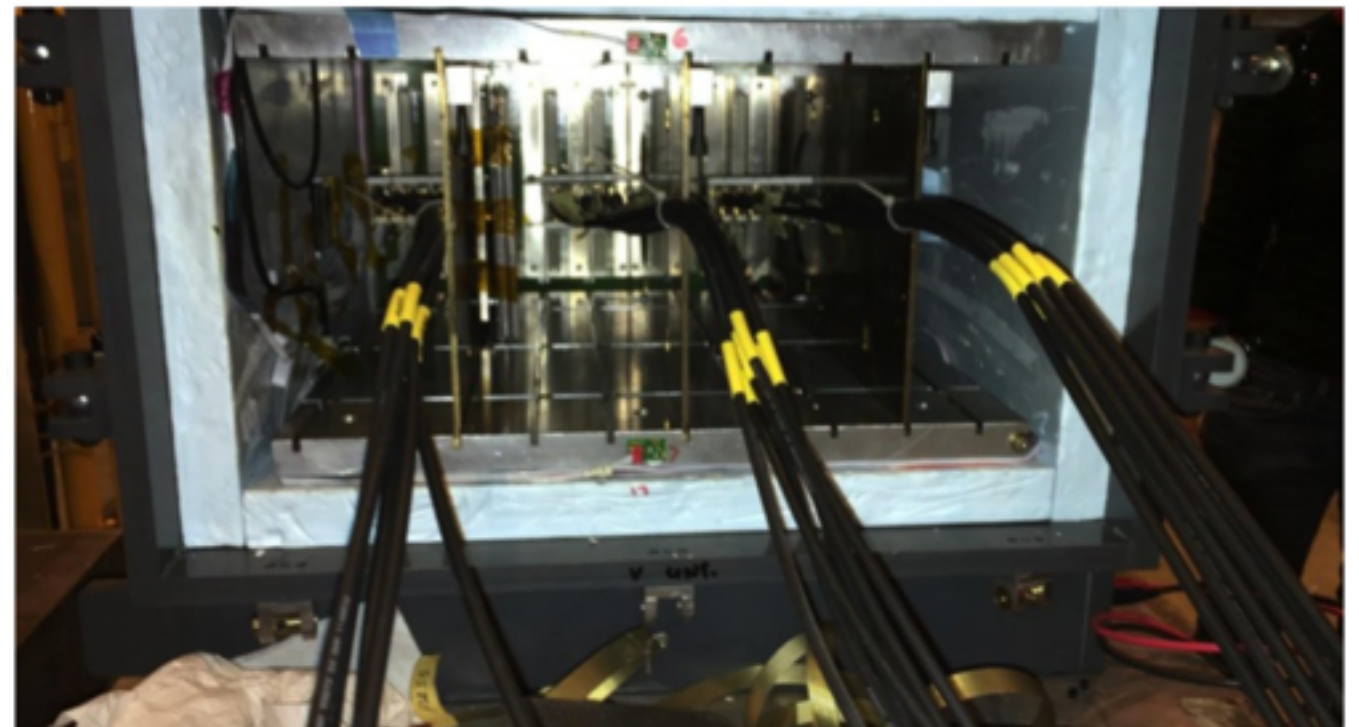
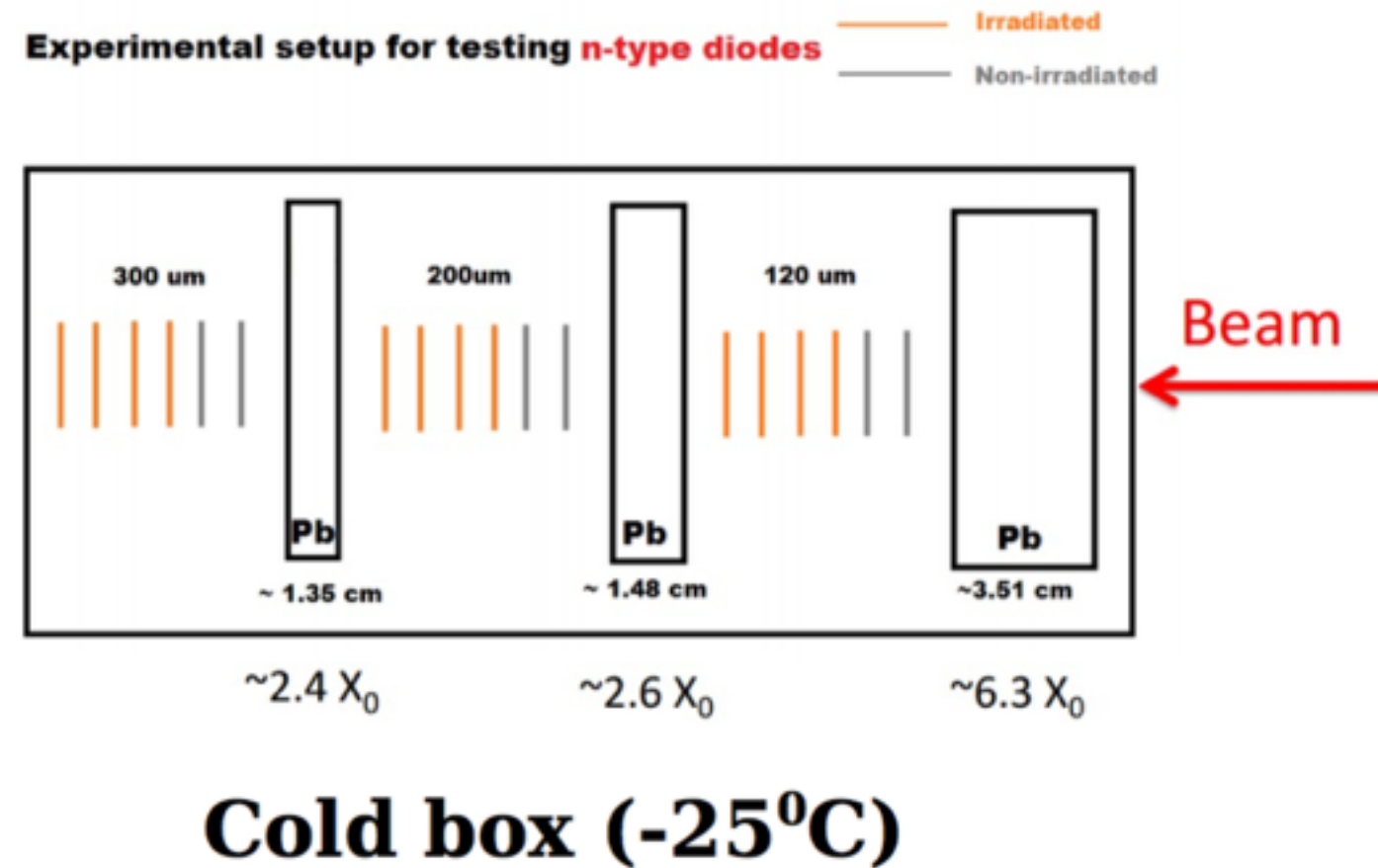
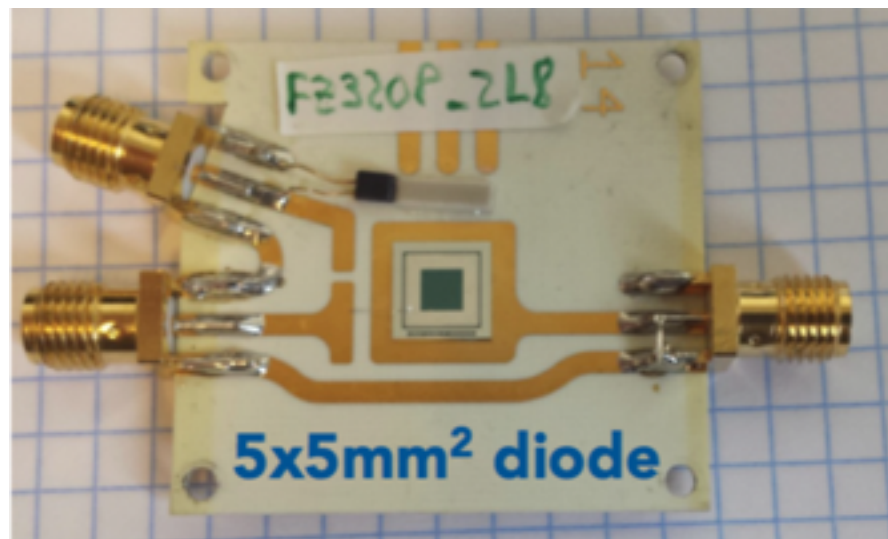


- Leakage current normalized by the volume of the diode is proportional to the fluence, even at high fluences
- The alpha measured at 800V is equal to the value measured during the CMS tracker upgrade with proton irradiation, $5.3 \times 10^{-17} \text{ A/cm}^3$ in both cases (scaled to +20°C) and consistent with Moll's thesis alpha value

- P type dd-FZ diodes of 320μm thickness showed significantly lower signals than N type diodes (under investigation), while similar for other thicknesses
- Signals from Epi (100μm) diodes are larger after radiation than from dd-FZ (120μm) diodes

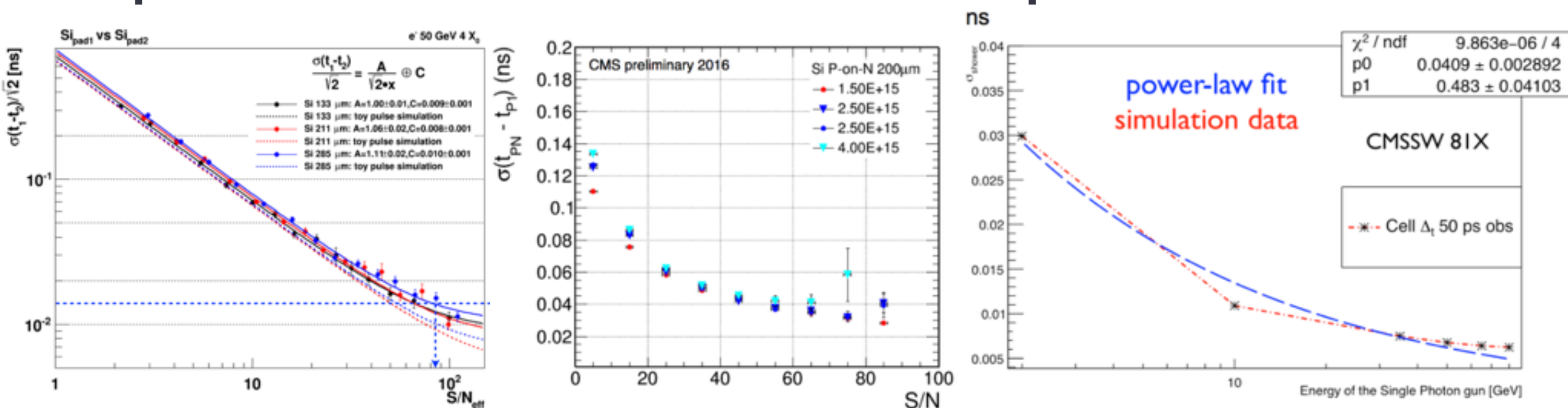
Timing Studies of Diodes at CERN

- **Goal:** to measure intrinsic timing capabilities of silicon detectors for EM showers
- **Study** time resolution as a function of signal amplitude, active thickness and fluence
- **Used** Cividec amplifiers and Caen V1742 fast (5GHz) digitizer with >500MHz bandwidth



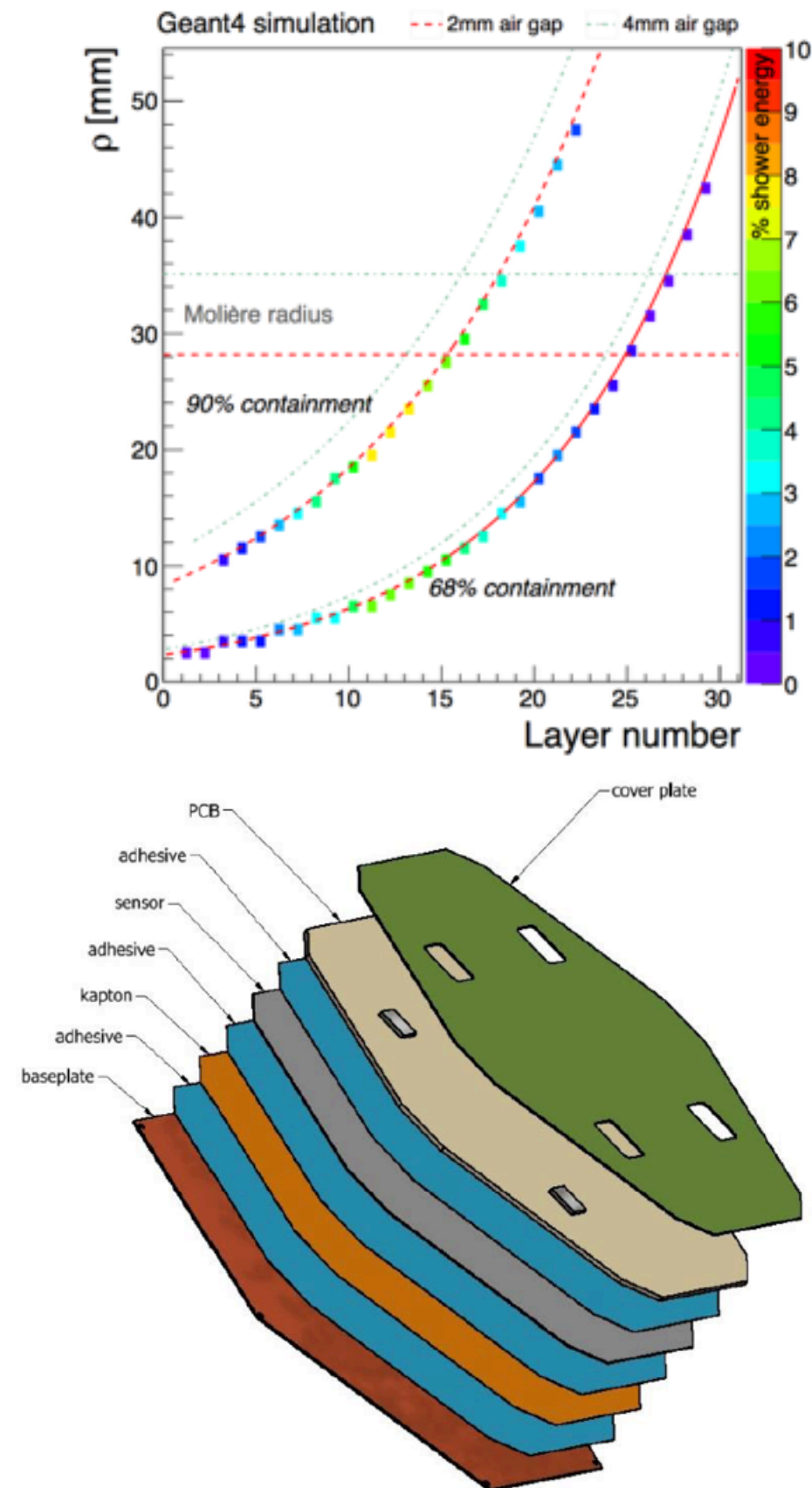
Timing Results

- Time resolution is measured by comparing time of signal arrival from two Si diodes, event by event
- Time resolution is determined by S/N
 - Dependence on sensor thickness is via S/N
 - Dependence on fluence is also via S/N
- Timing resolution is $< 20\text{ps}$ for $\text{S/N} > 50$
- Application of timing capabilities of silicon sensors may resolve showers in time and help mitigate pile-up at HL-LHC
- $\sim 10\text{ps}$ resolution for EM shower with 50ps cell resolution



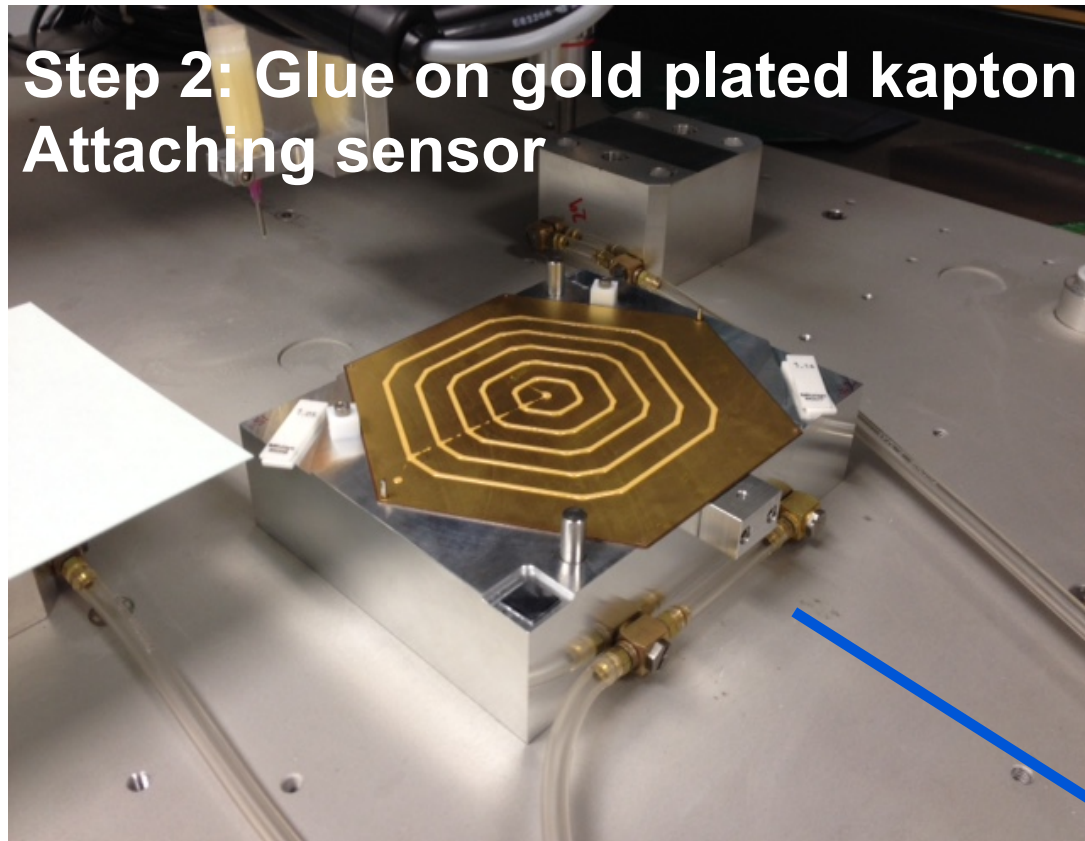
Module Design and Construction

- The electromagnetic part of HGCal requires compact construction to keep shower size small
- Module design is being optimized
 - to obtain low profile
 - requires as thin as possible electronics design
 - wire-bonding sensor cells to PCB requires
 - meeting tight gluing tolerances to ensure the PCB is flat, horizontal ($\sim 100\mu\text{m}$) and well supported by the glue
 - good alignment ($\sim 100\mu\text{m}$) of sensor and PCB layers
 - may require deep access wire-bonding machine ($\sim 1\text{mm}$ deep)

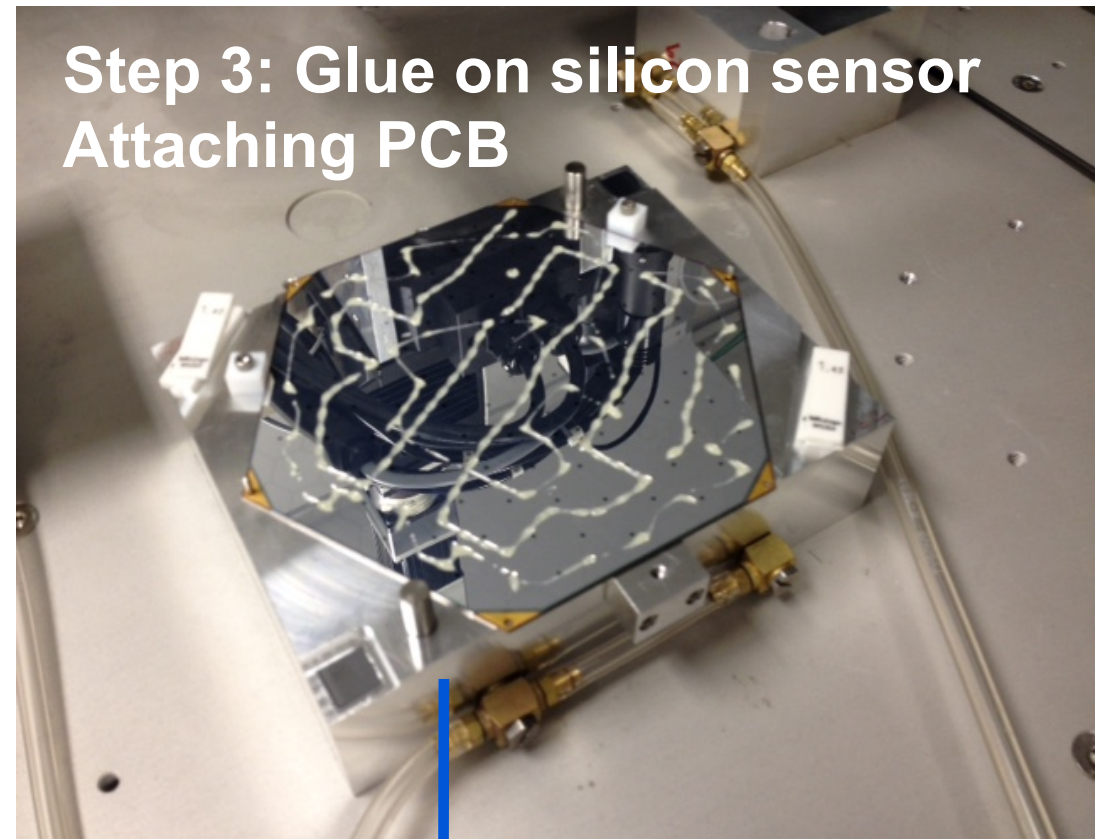


Module Assembly

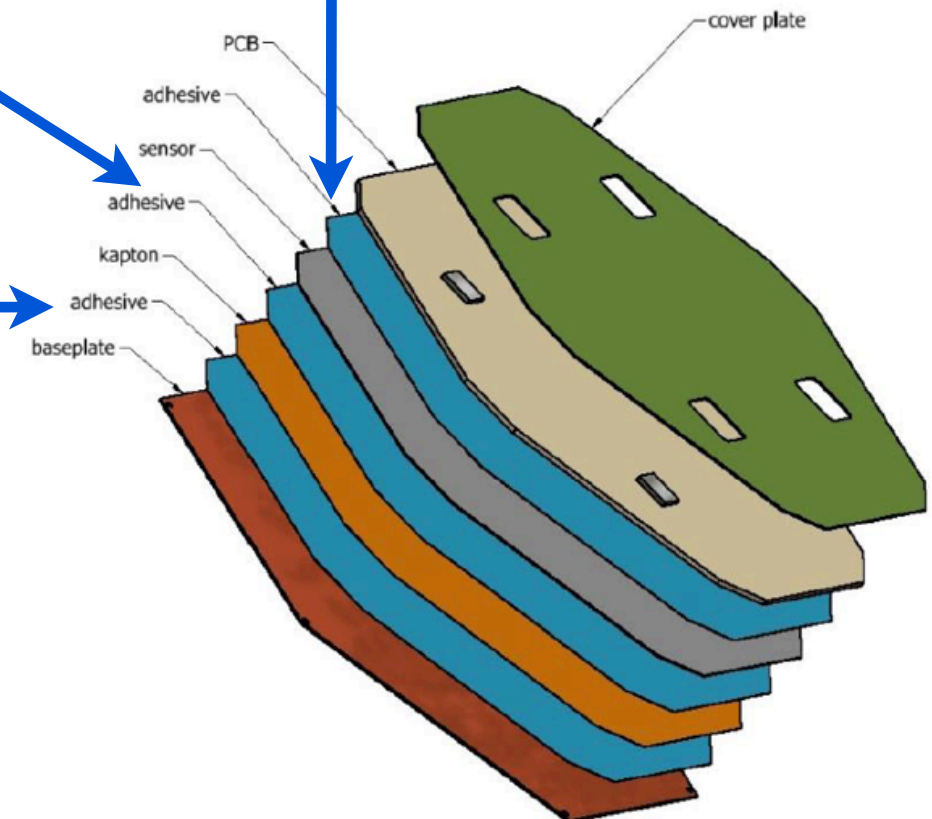
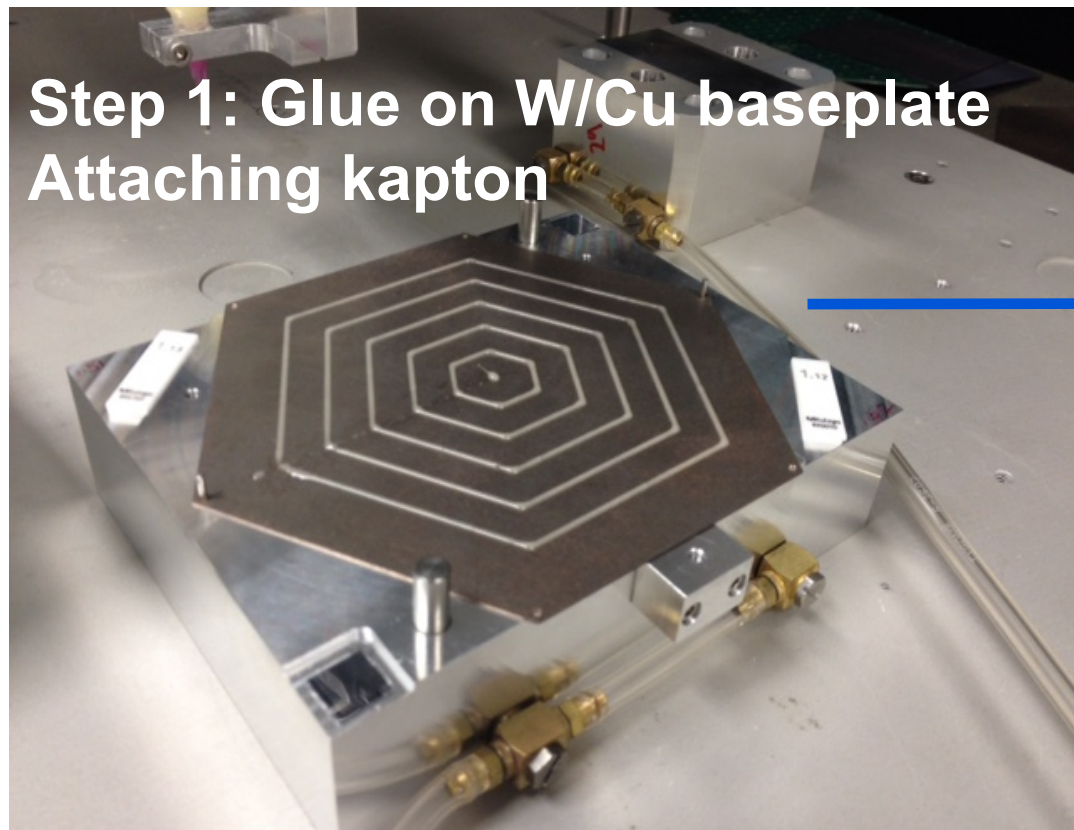
**Step 2: Glue on gold plated kapton
Attaching sensor**



**Step 3: Glue on silicon sensor
Attaching PCB**

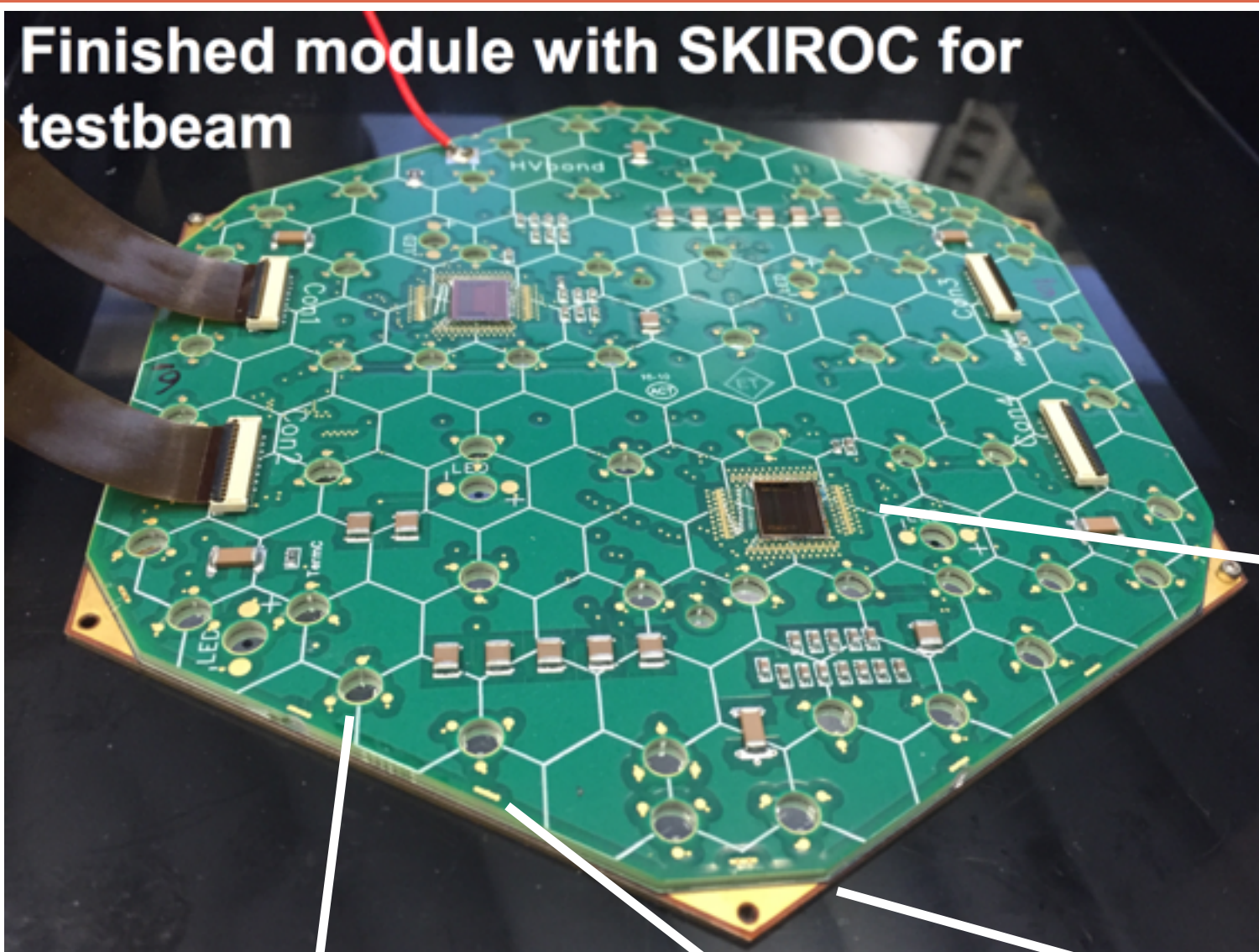


**Step 1: Glue on W/Cu baseplate
Attaching kapton**

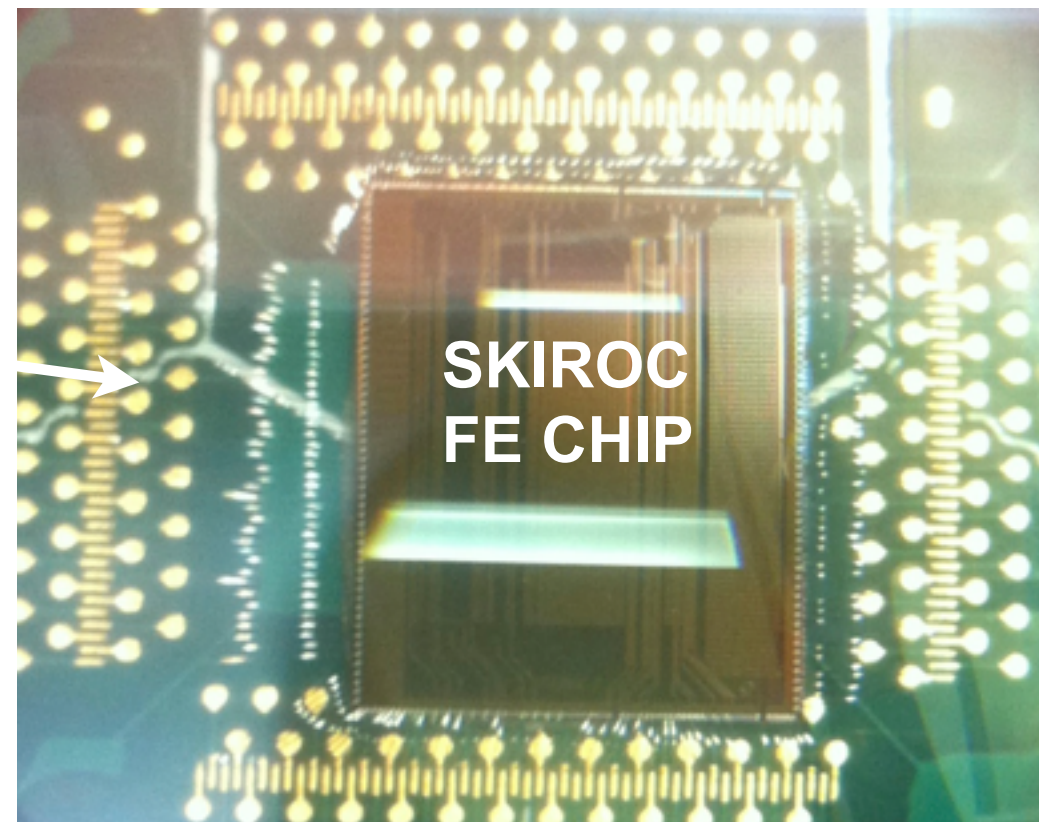


Wire Bonding

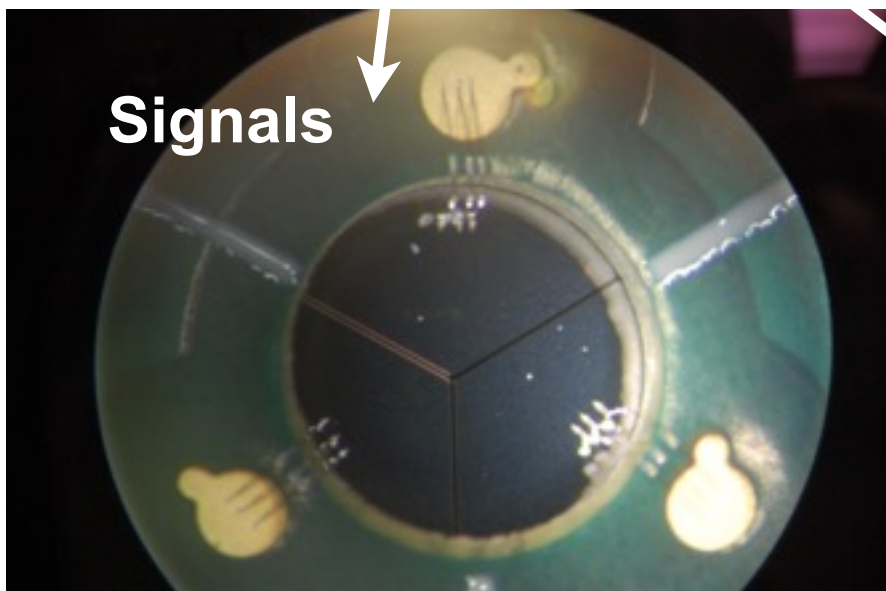
Finished module with SKIROC for testbeam



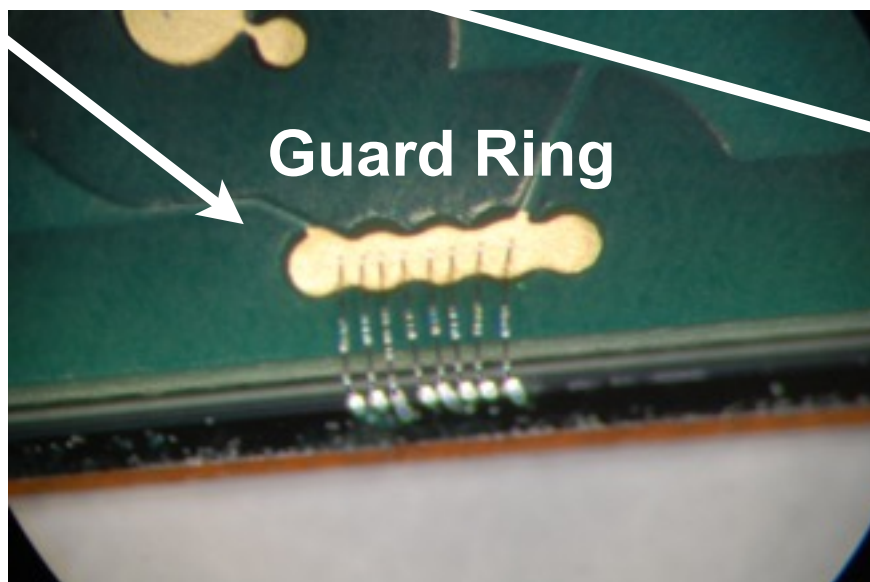
- **~ 700 wire bonds on a single module!**



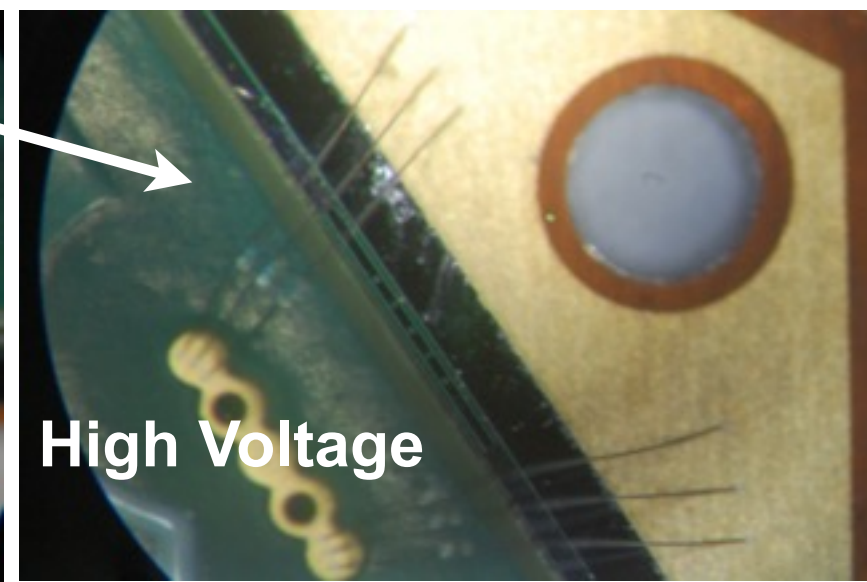
Signals



Guard Ring

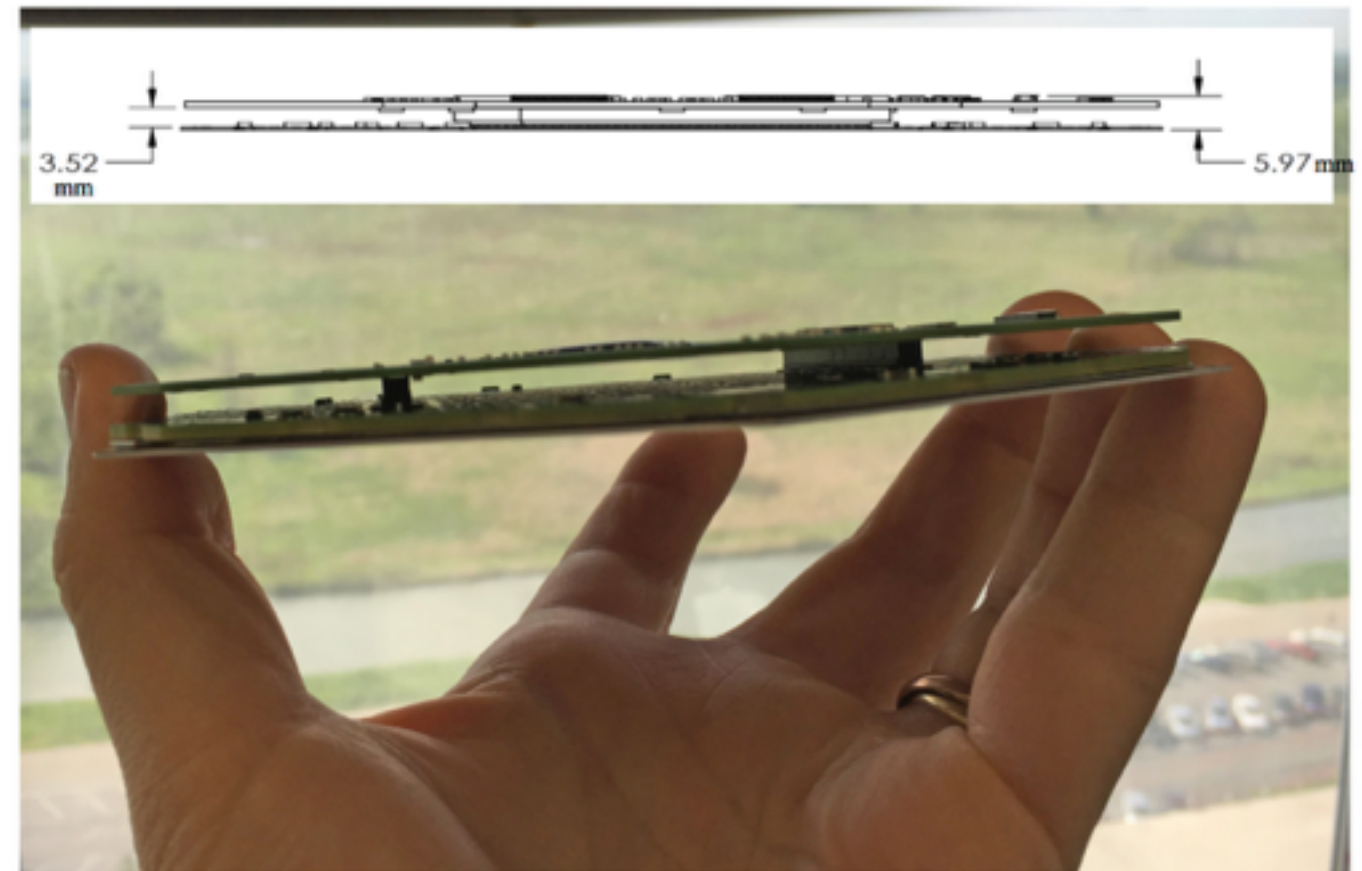
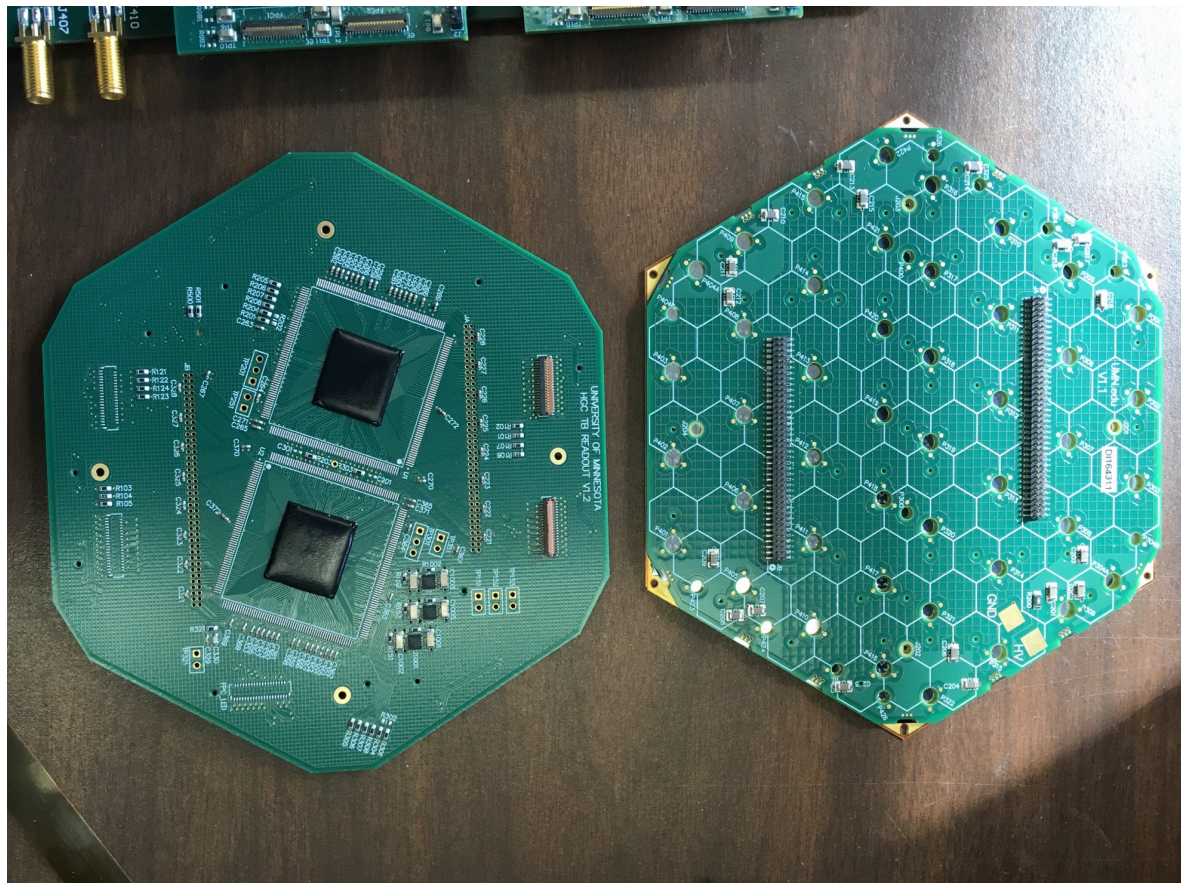


High Voltage



Double-layer Module Prototype

- **In parallel, a double-layer module structure has been explored**
 - bottom layer is a passive PCB connecting silicon pads to a connector
 - top layer carries all electronics, SKIROC chips, etc...
 - allows replacement of electronics and reuse of the sensors during R&D
 - Successfully operated in test beams



Automated Assembly of Modules

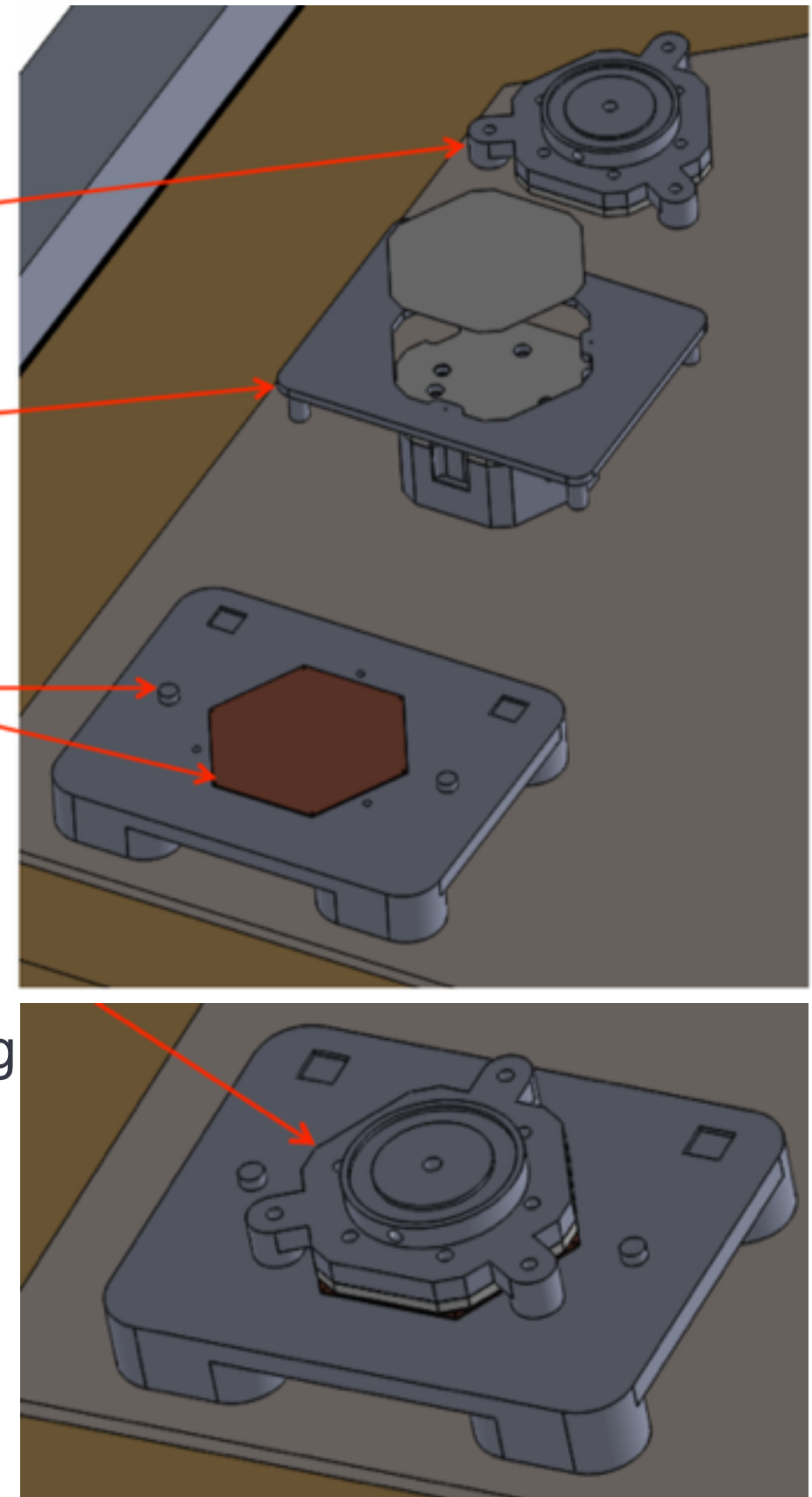
- **Setting up Gantry machine for automated assembly of modules**
- **Reproducible results**
- **High rate and volume of assembly**
- **Will be tested for the production of the test beam prototype calorimeter**

Clamping tool

Sensor holding tray

Baseplate on carrier tray

Assembled module cures under clamping tool



Overview of Beam Tests

- **Goals**

- verify functionality of design with a full depth but narrow calorimeter prototype
- performance studies: signal to noise, timing, energy and position resolutions

- **Several beam tests at FNAL and CERN**

- FNAL: 120GeV protons, 4-32GeV electrons/pions
- CERN: 125GeV pions, 20-250 GeV electrons

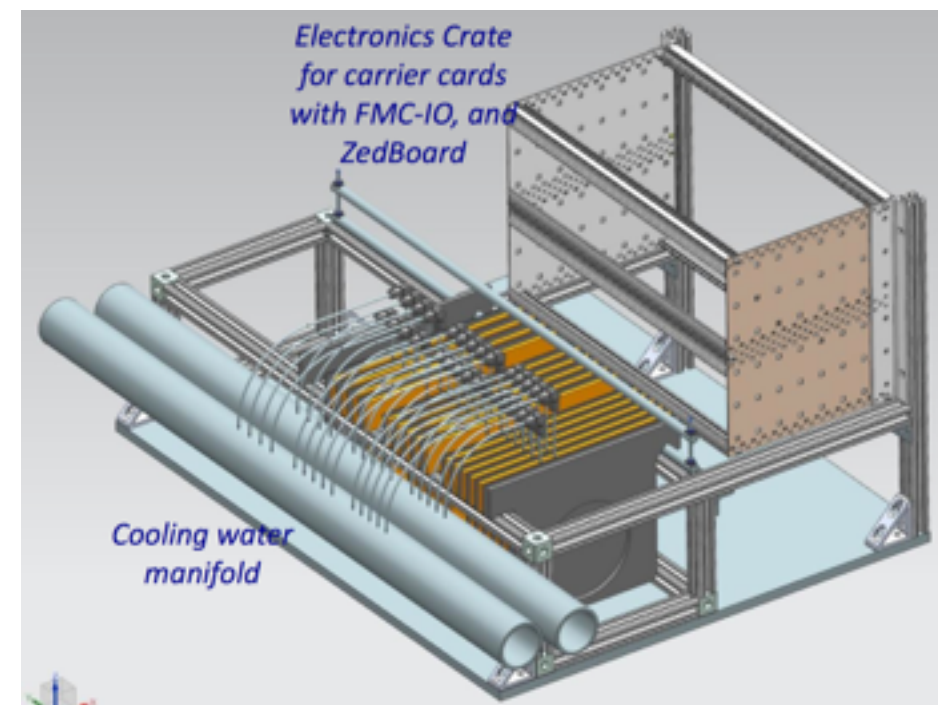
- **Each layer contains 1 sensor mounted on a copper cooling plate**

- 6", 200um active thickness, p-on-n, 1.1cm² cell size

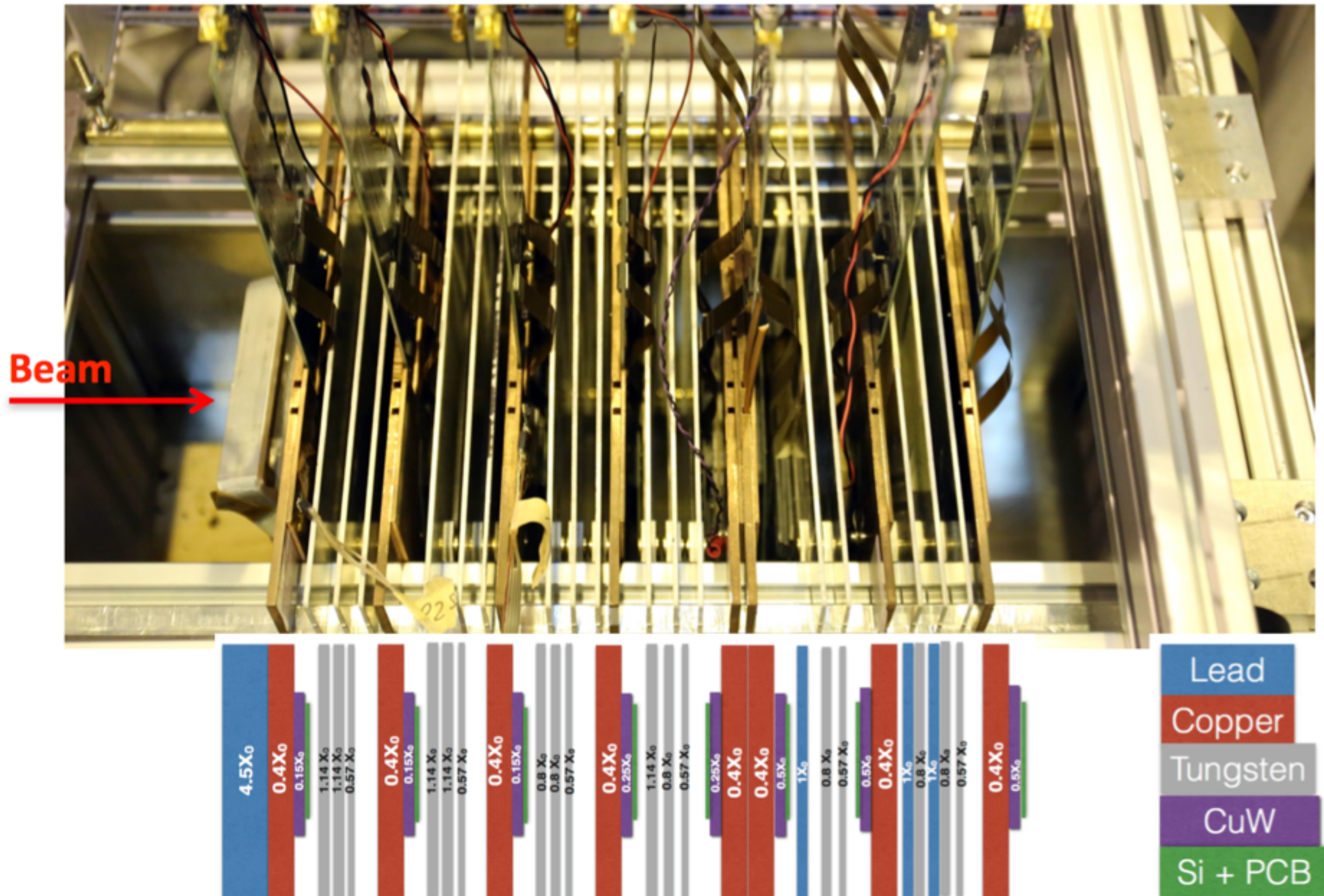
- **Hanging file design for mechanical structure**

- Flexible insertion of absorbers and modules on cooling plates

Laboratory	Layers	Rad length	Date
FNAL	1	6	March 2016
FNAL	4	12	May 2016
FNAL	16	15	July 2016
CERN	8	27	Aug 2016



Cern Test Beam (27 X_0 with 8 Layers)

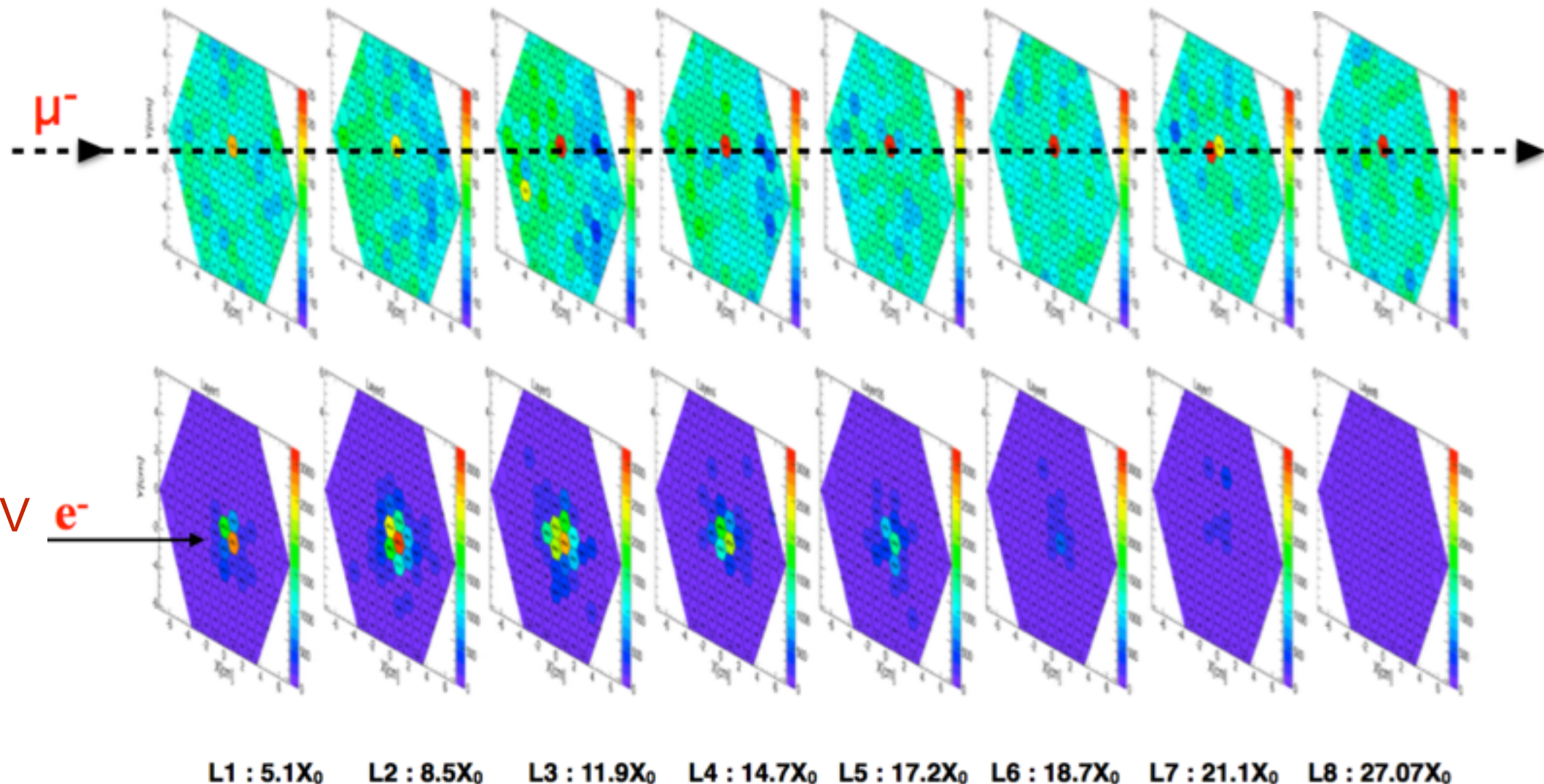
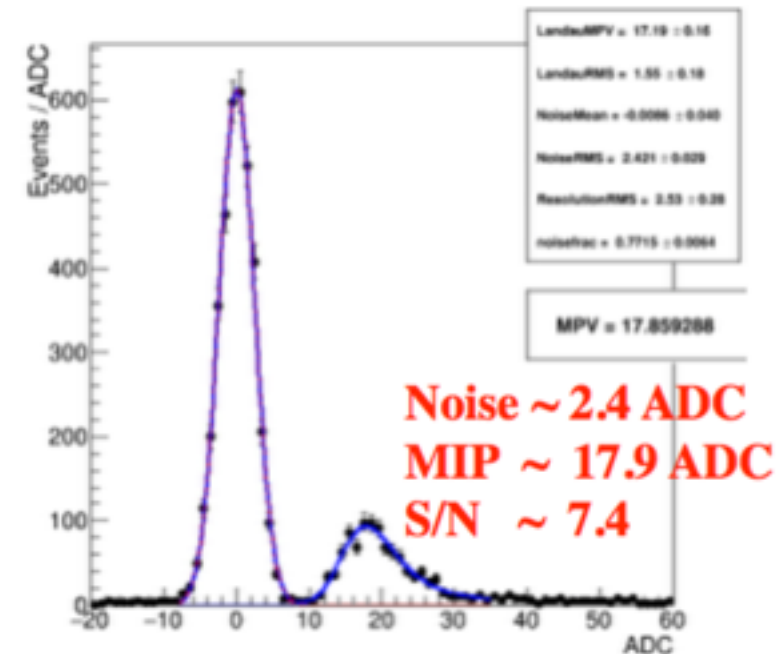


Calibration and Event Displays

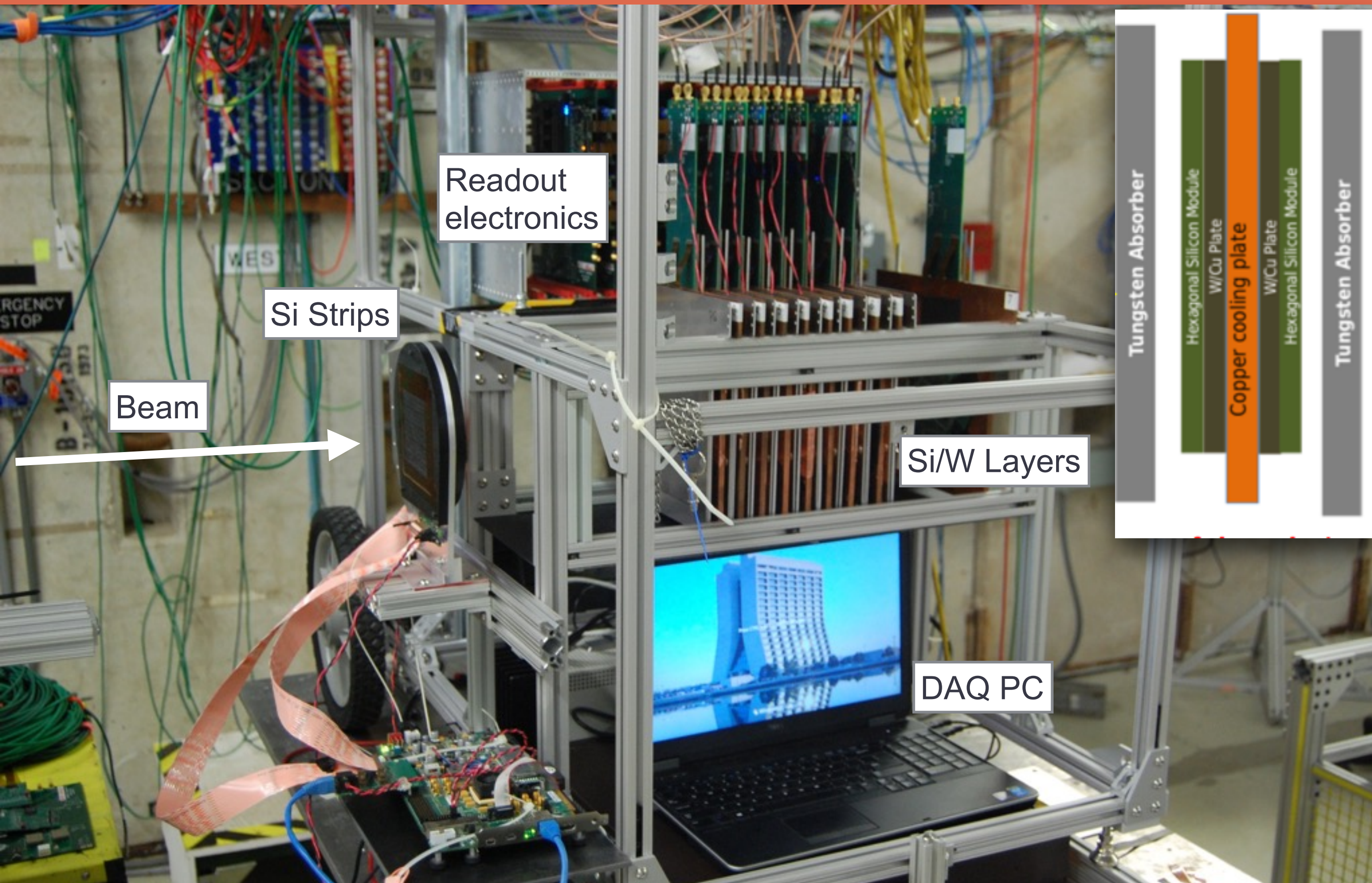
- **Muon beam used to calibrate sensors**

- After pedestal and coherent noise subtraction distribution of ADC counts is fit with a Landau distribution convoluted with a Gaussian
- 1 MIP ~ 17.9 ADC

- **Detailed analyses of data ongoing**

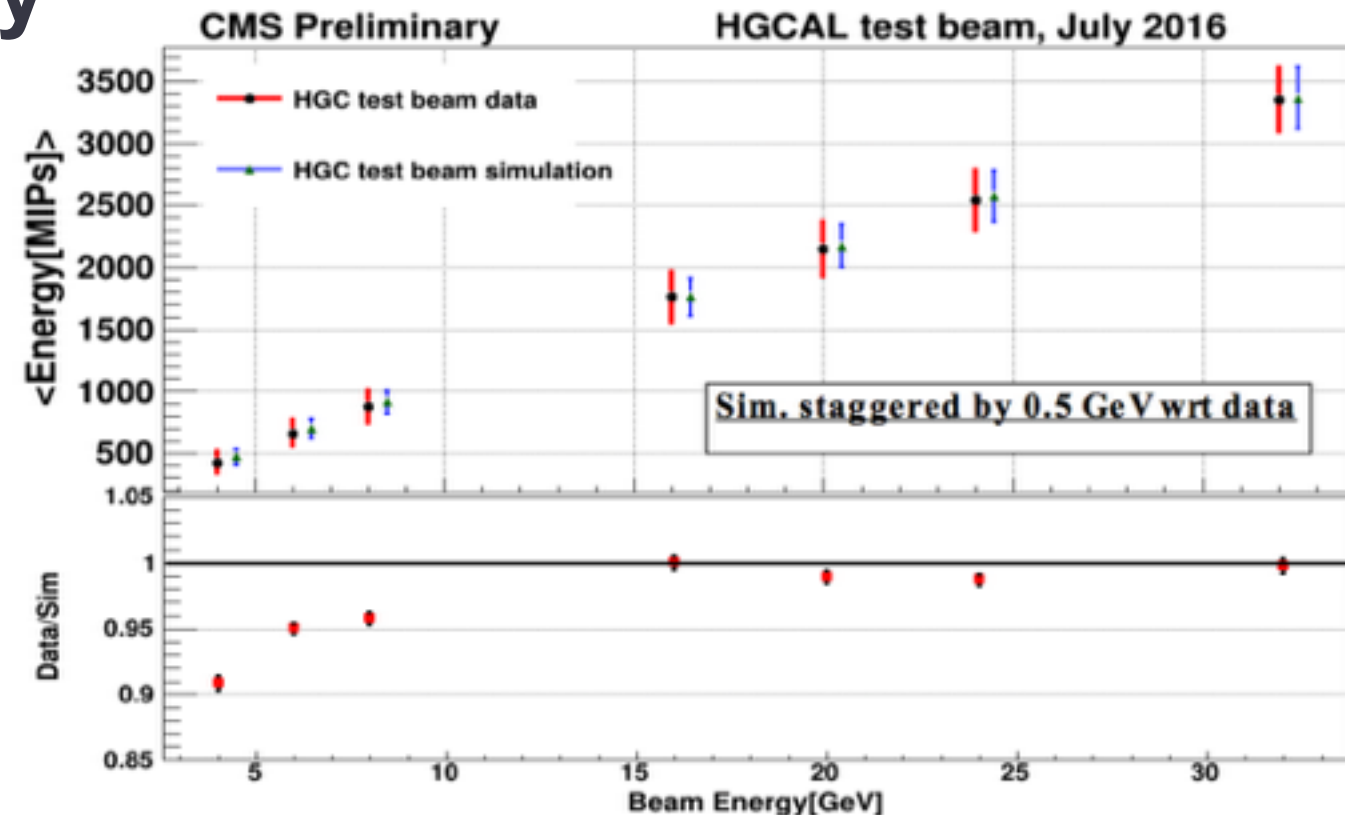
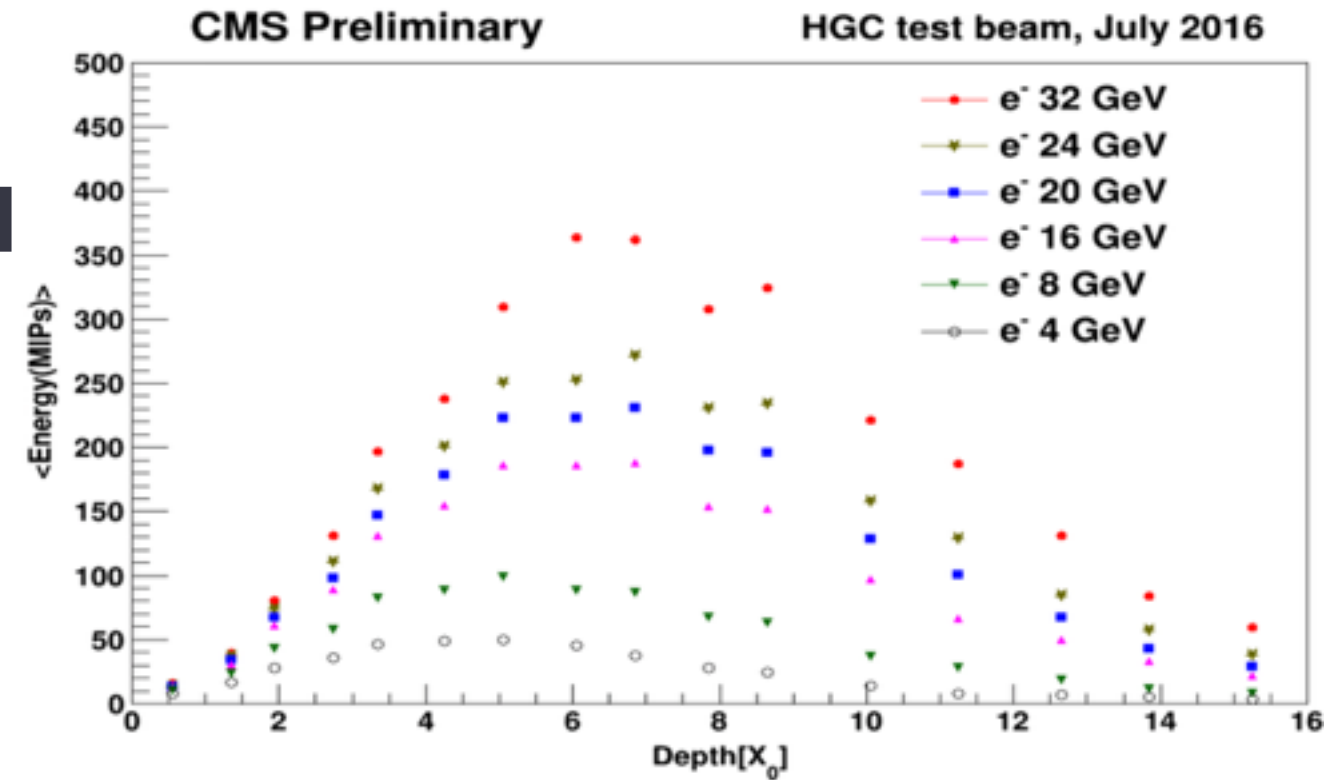


Fermilab Test Beam (15 X_0 with 16 Layers)



Energy Depositions and MC Comparisons

- All layers have been calibrated
- Pedestals and noise subtracted
- Top plot shows energy deposited in each layer
 - Shower max moves to higher depth with increasing electron beam energy, as expected
- Bottom plot shows total energy deposited in all layers as a function of e^- beam energy
 - Dependence is linear
 - Compared to Geant 4 simulation
 - Good agreement ($\sim 5\%$) observed



Summary

- **CMS is preparing for a High Granularity Endcap calorimeter largely based on silicon sensors, (600m² and 6M channels)**
- **First prototype HGCal sensors have been fabricated and show excellent quality and expected performance**
 - comprehensive suite of studies is planned and well underway
- **Radiation studies of silicon diodes show good radiation hardness for entire lifetime of HL-LHC (3000fb⁻¹)**
- **Good intrinsic timing resolution (<20ps at high enough S/N) of silicon diodes has been measured. This can help mitigate the effect of pileup and in localizing the primary vertex of the event of interest.**
- **Construction of prototype modules has been successfully demonstrated and work started on automated assembly**
- **Successfully constructed and operated a 16 layer EE prototype in the test beam**

Additional Material

Strategy for FE Electronics

1) Modify existing CALICE chip to include most of the required functionalities

Exercise functionalities such as ToT, cross calibration ADC-ToT, fast timing...

Allows study of FE printed circuit board and module assembly

Test beams 2016-2017

 **Omega**

SKIROC2 -> SKIROC2-CMS 0.35 μm AMS (non radhard)

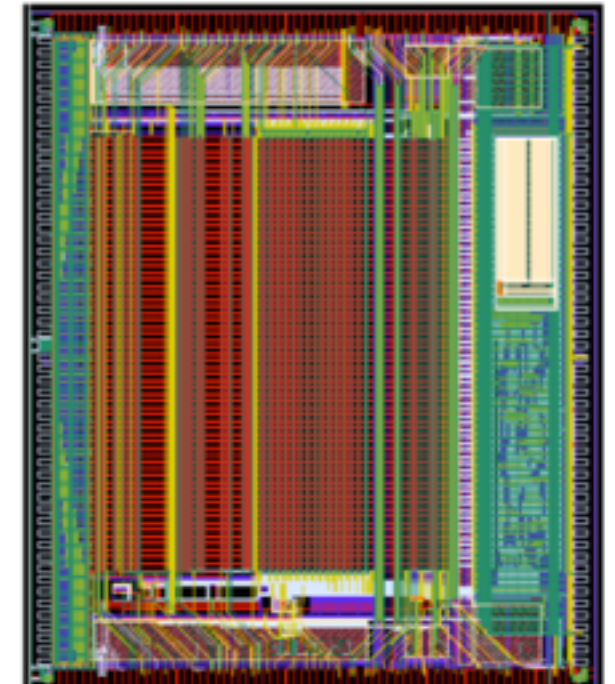
faster shaper 25ns instead of 200 ns

sampling @ 40 MHz, depth 300 ns

ToT

TDC for ToA, 20 ps binning, 50 ps jitter

Received late June, under test (see next presentation)



2) Submit Test Vehicles in 130 nm

TV1 *received* mid-September: analogue architecture, baseline + variants

TV2 to be submitted before end 2016: 8 channels, analogue+ADC+ToT+ Trigger sums

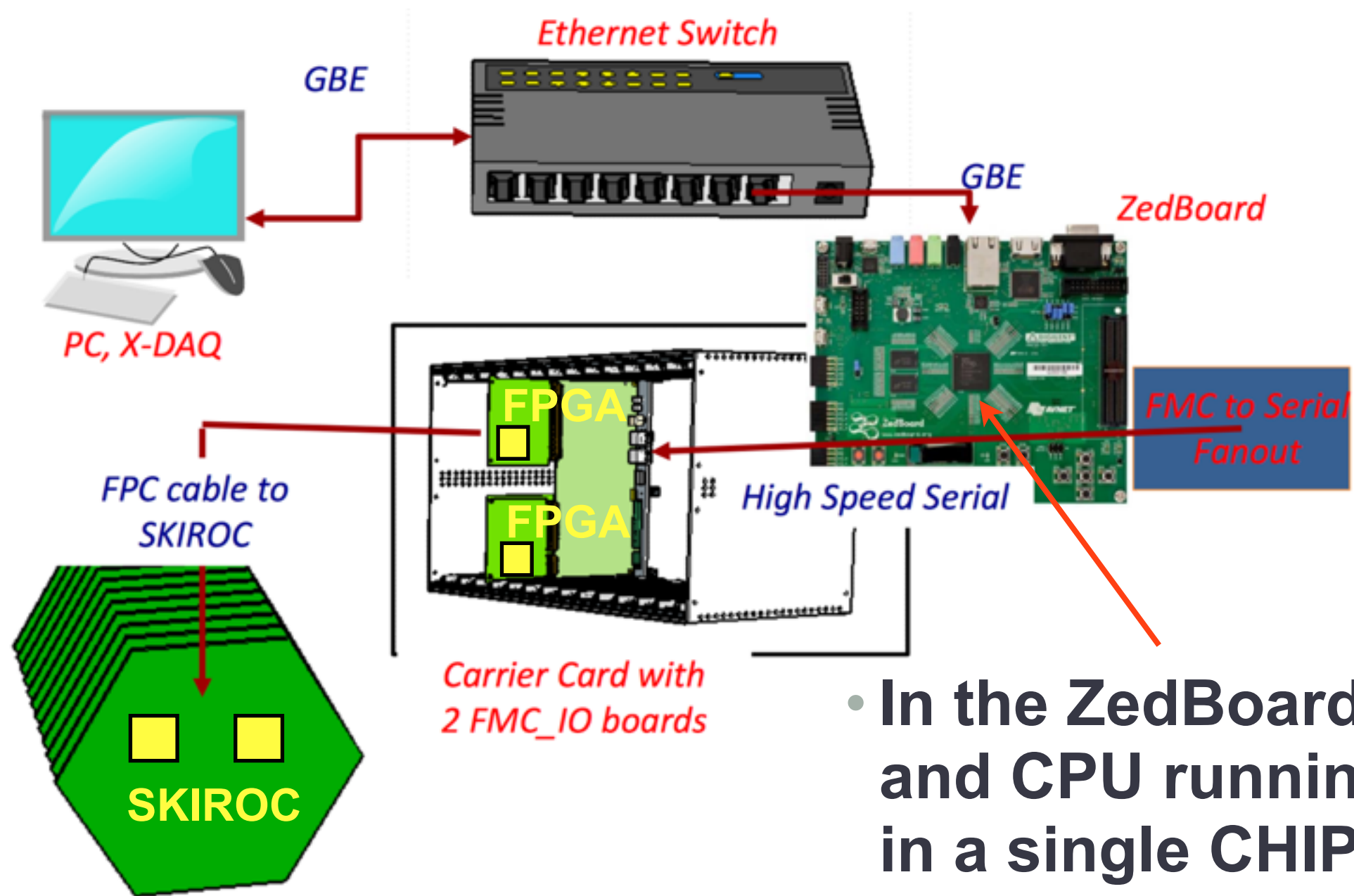
3) Submit first “complete” ASIC June 2017

(some digital functionalities may still be incomplete)

4) Two more iterations foreseen in the overall planning

16

Test Beam DAQ



- In the ZedBoard: FPGA and CPU running Linux in a single CHIP
- Allows easy transfer of data from FPGAs to Computers